

# Fundamentals of Analog & Mixed Signal VLSI Design

## Continuous-Time Filters (CTF)

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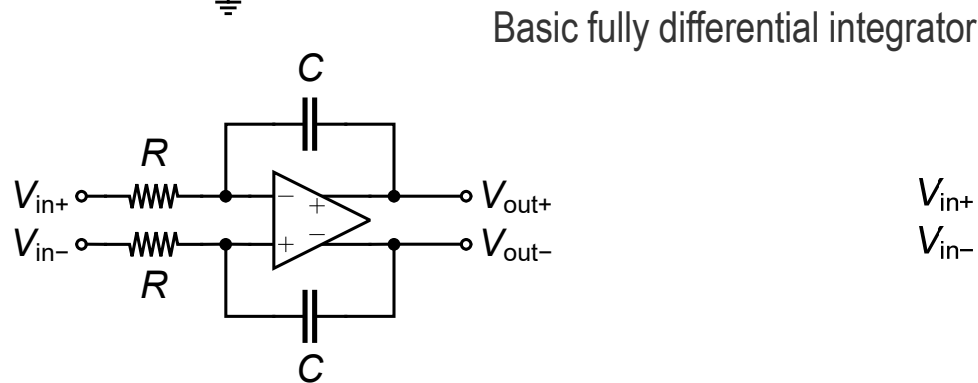
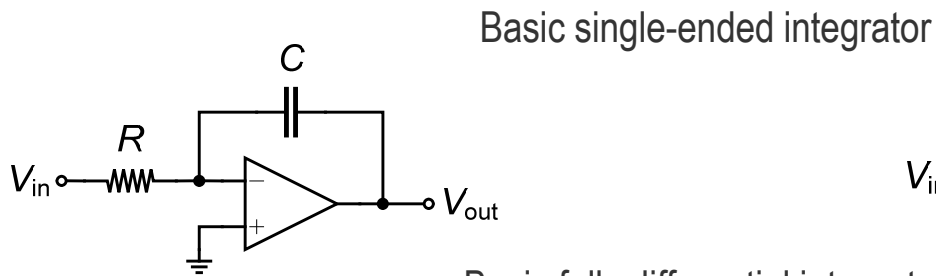
The logo of the Swiss Federal Institute of Technology, Lausanne (EPFL), consisting of the letters 'EPFL' in a bold, red, sans-serif font.

# Outline

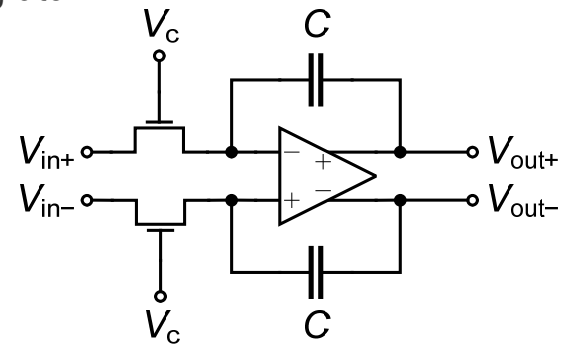
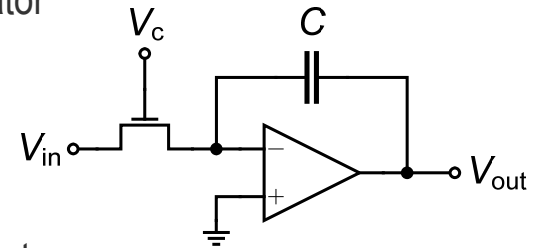
- **Introduction**
- RC-active filters
- MOSFET-C filters
- $G_m$ -C filters
- Source-follower CTFs
- Noise in CTFs
- Automatic tuning

# Different Types of CTFs – Active RC and MOSFET-C

## Active RC



## MOSFET-C

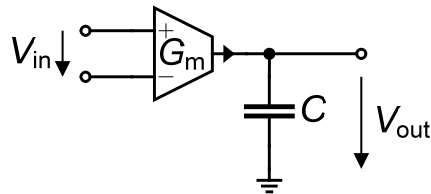


- + Good linearity
- + Small number of active elements
- + Insensitive to parasitics
- Must drive low impedance loads
- No continuous-time tuning mechanism

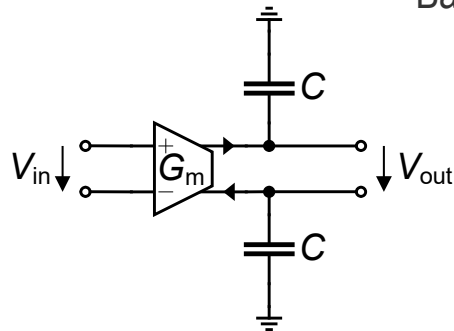
- + Insensitive to parasitics
- + Small number of active elements
- Must drive low impedance loads
- Nonlinearity of MOS resistance

# Different Types of CTFs – $G_m$ -C and $G_m$ -OPAMP-C

## $G_m$ -C

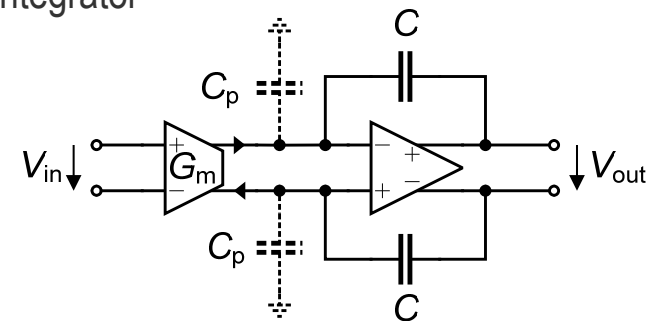
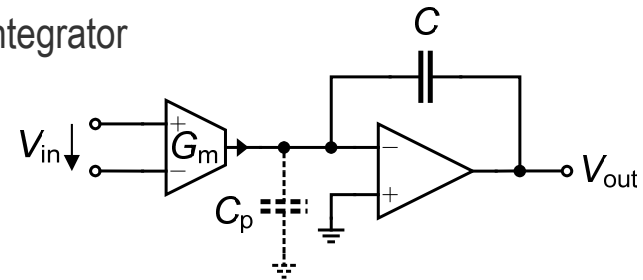


Basic single-ended integrator



Basic fully differential integrator

## $G_m$ -OPAMP-C



- + Fastest of all approaches
- + No need to drive low impedance loads
- Sensitive to parasitic capacitances
- Nonlinearity of transconductor

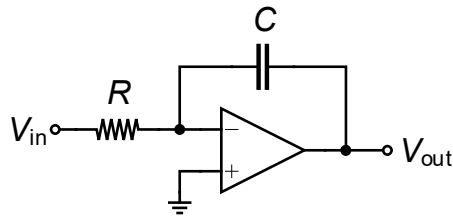
- + Insensitive to parasitic capacitances
- + No need to drive low impedance loads
- + Small output swing transconductors
- Largest number of active elements
- Additional poles → slow

# Outline

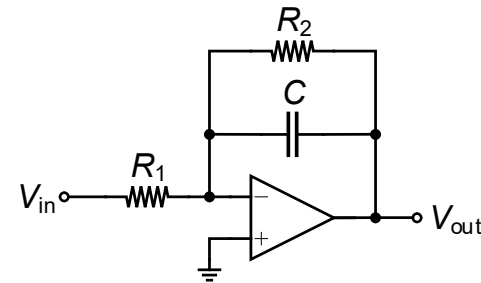
- Introduction
- **RC-active filters**
- MOSFET-C filters
- $G_m$ -C filters
- Source-follower CTFs
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- Automatic tuning

# Active-RC Filters

Integrator



$$T(s) \triangleq \frac{V_{out}}{V_{in}} = -\frac{1}{s\tau} \text{ with } \tau = RC$$

1<sup>st</sup>-order low-pass filter

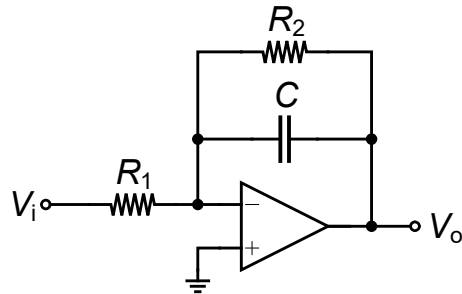
$$T(s) \triangleq \frac{V_{out}}{V_{in}} = \frac{K}{1 + \frac{s}{\omega_c}}$$

$$\text{with } K = -\frac{R_2}{R_1} \text{ and } \omega_c = \frac{1}{R_2 C}$$

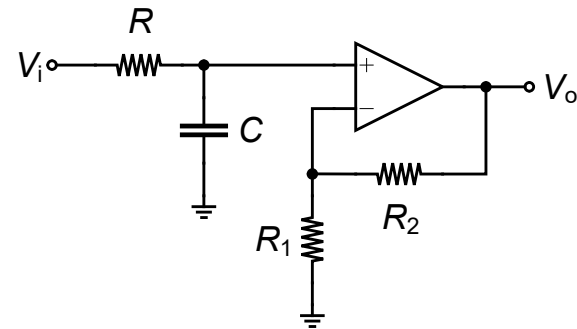
- Assuming the OPAMP gain is large enough, active-RC filters offer
  - ▶ **good linearity**
  - ▶ **low sensitivity to the parasitic input capacitance**  
(however the cut-off frequency may depend on the load capacitance)
- On the other hand they must drive low impedance loads which leads to **higher power consumption**

# First-order LP Sections

## Inverting



## Noninverting



- The transfer function is given by

$$T(s) \triangleq \frac{V_o}{V_i} = K \frac{\omega_c}{s + \omega_c}$$

- with  $K = -\frac{R_2}{R_1}$  and  $\omega_c = \frac{1}{R_2 C}$
- Notice that the **dc gain  $K$  is negative**

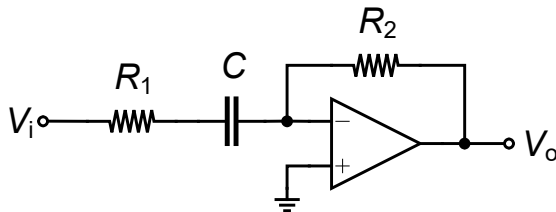
- The alternative 1<sup>st</sup>-order section shown above does not introduce any inversion ( **$K$  positive**)

$$T(s) \triangleq \frac{V_o}{V_i} = K \frac{\omega_c}{s + \omega_c}$$

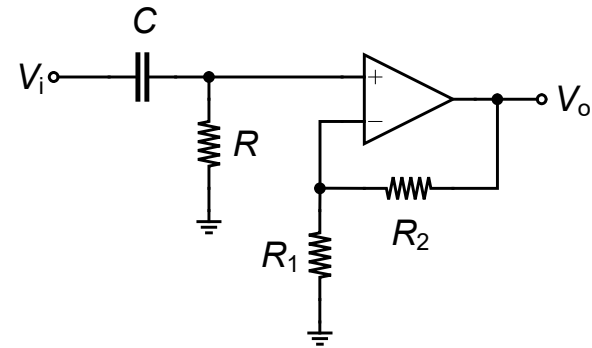
- with  $K = 1 + \frac{R_2}{R_1}$  and  $\omega_c = \frac{1}{RC}$

# First-order HP Sections

Inverting



Noninverting



- The transfer function is given by

$$T(s) \triangleq \frac{V_o}{V_i} = K \frac{s}{s + \omega_c}$$

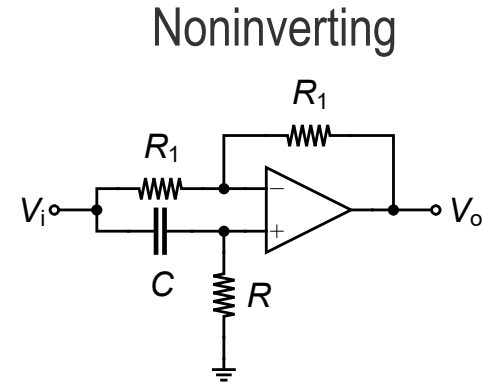
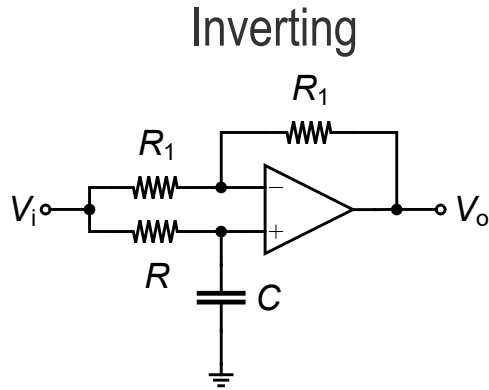
- with  $K = -\frac{R_2}{R_1}$  and  $\omega_c = \frac{1}{R_1 C}$

- The alternative 1<sup>st</sup>-order section shown above does not introduce any inversion in the passband

$$T(s) \triangleq \frac{V_o}{V_i} = K \frac{s}{s + \omega_c}$$

- with  $K = 1 + \frac{R_2}{R_1}$  and  $\omega_c = \frac{1}{RC}$

# First-order All-pass Sections



- The transfer function is given by

$$T(s) \triangleq \frac{V_o}{V_i} = K \frac{s - \omega_c}{s + \omega_c}$$

- with  $K = -1$  and  $\omega_c = \frac{1}{RC}$

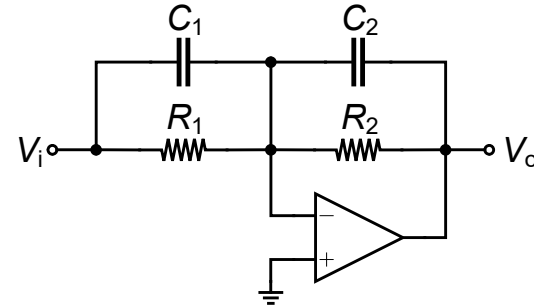
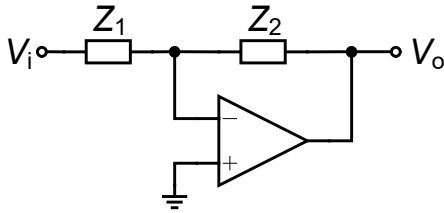
- The alternative 1<sup>st</sup>-order section shown above has the same transfer function

$$T(s) \triangleq \frac{V_o}{V_i} = K \frac{s - \omega_c}{s + \omega_c}$$

- except that now the gain is positive

$$K = +1 \text{ and } \omega_c = \frac{1}{RC}$$

# First-order Filters Based on the Inverting Amplifier



- Other 1<sup>st</sup>-order transfer functions can be obtained from the inverting amplifier using impedances  $Z_1$  and  $Z_2$
- The transfer function is then given by

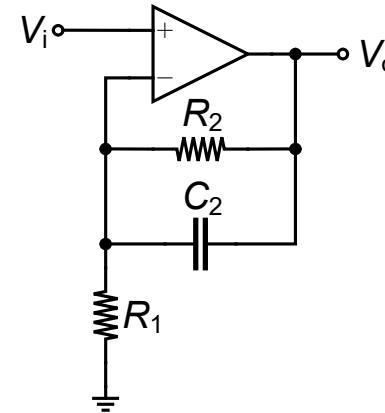
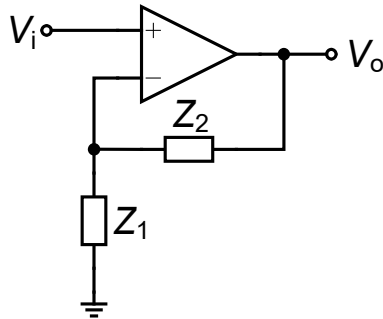
$$T(s) \triangleq \frac{V_o}{V_i} = -\frac{Z_2}{Z_1} = -\frac{Y_1}{Y_2}$$

- For example replacing  $Z_1$  and  $Z_2$  by parallel RC leads to

$$T(s) \triangleq \frac{V_o}{V_i} = K \frac{s + \omega_z}{s + \omega_c}$$

- with  $K = -\frac{C_1}{C_2}$ ,  $\omega_z = \frac{1}{R_1 C_1}$  and  $\omega_c = \frac{1}{R_2 C_2}$

# First-order Filters Based on the Noninverting Amplifier



- The noninverting amplifier can be used if positive gain is needed
- The transfer function is then given by

$$T(s) \triangleq \frac{V_o}{V_i} = 1 + \frac{Z_2}{Z_1} = 1 + \frac{Y_1}{Y_2}$$

- The transfer function of the above circuit is given by

$$T(s) \triangleq \frac{V_o}{V_i} = K \frac{s + \omega_z}{s + \omega_c}$$

- with  $K = 1 + \frac{R_2}{R_1}$ ,  $\omega_z = \frac{1}{C_2} \left( \frac{1}{R_1} + \frac{1}{R_2} \right)$   
and  $\omega_c = \frac{1}{R_2 C_2}$

# The General Second-order Filter Function

- The second-order filter function, in its general form, is the following

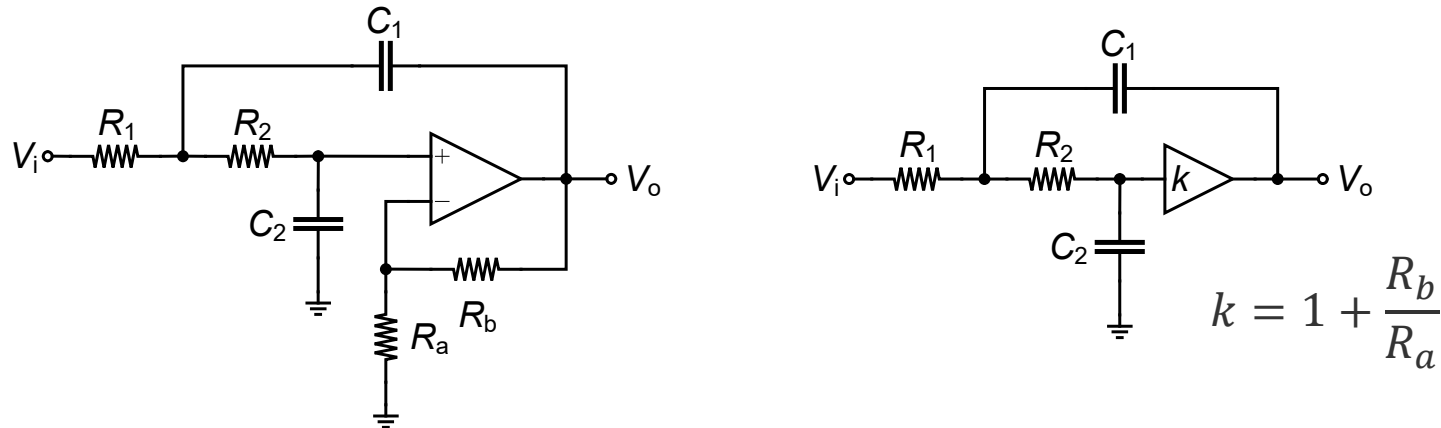
$$T(s) = \frac{a_2 s^2 + a_1 s + a_0}{s^2 + b_1 s + b_0}$$

- Realization of this function using active RC networks is of interest only in the case that  $\sqrt{b_0} > 0.5 b_1$ , i.e. when the poles of  $T(s)$  are **complex conjugate**
- $T(s)$  can be written alternatively in the general “**biquadratic**” (or **biquad**) form as

$$T(s) = K \frac{s^2 + \frac{\omega_z}{Q_z} s + \omega_z^2}{s^2 + \frac{\omega_p}{Q_p} s + \omega_p^2}$$

- where  $\omega_z$  and  $\omega_p$  are the undamped **natural** (or **resonance**) **frequencies** of the zeros and poles respectively, while  $Q_z$  and  $Q_p$  are the corresponding **quality factors**, or Q-factors
- The zero or pole frequency is the magnitude of the zero or pole, respectively, while their quality is a measure of how near the corresponding zero or pole are to the  $j\omega$ -axis in the s-plane

# The Sallen-Key Single OPAMP Second-order LP Filter



- The most popular single OPAMP 2<sup>nd</sup>-order **LP** circuit is that of **Sallen-Key** shown above, which uses a noninverting amplifier with a **single OPAMP**
- Its transfer function is given by

$$T(s) \triangleq \frac{V_o}{V_i} = \frac{k/(R_1 R_2 C_1 C_2)}{s^2 + \left( \frac{1}{R_1 C_1} + \frac{1}{R_2 C_1} + \frac{1-k}{R_2 C_2} \right) s + \frac{1}{R_1 R_2 C_1 C_2}} = \frac{K}{s^2 + \frac{\omega_p}{Q_p} s + \omega_p^2}$$

- where  $k = 1 + R_b/R_a$  is the dc gain of the noninverting amplifier

# The Sallen-Key Single OPAMP Second-order LP Filter

- Identifying the coefficients gives the following **design equations**

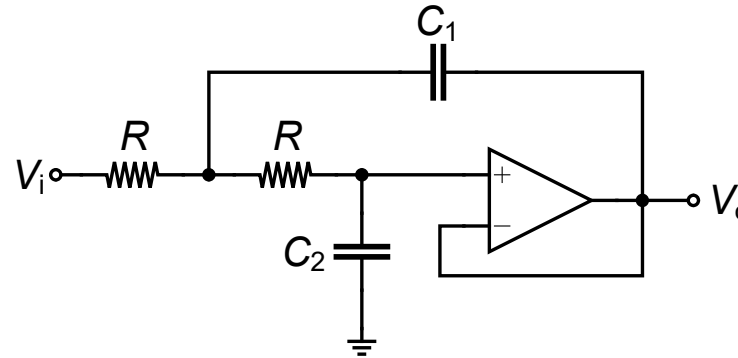
$$K = \frac{k}{R_1 R_2 C_1 C_2}, \omega_p = \frac{1}{\sqrt{R_1 R_2 C_1 C_2}}, Q_p = \frac{\sqrt{R_1 R_2 C_1 C_2}}{C_2 (R_1 + R_2) + R_1 C_1 (1 - k)}$$

- with  $k = 1 + \frac{R_b}{R_a}$
- Since the number of unknowns is larger than the number of equations, some components will have to be selected arbitrarily (or from other constraints)
- One popular choice is to choose  $k = 1$  ( $R_a = \infty$ ) which corresponds to operating the OPAMP as a **voltage follower** and hence use its **full bandwidth**
- The other resistances can then be selected equal, leading to

$$R_1 = R_2 = R, K = \omega_p^2 = \frac{1}{R^2 C_1 C_2}, \omega_p = \frac{1}{R \sqrt{C_1 C_2}}, Q_p = \frac{1}{2} \sqrt{\frac{C_1}{C_2}}$$

- The dc gain  $K / \omega_p^2$  is restricted to unity which is usually not a problem for filter design

# The Sallen-Key Single OPAMP Second-order LP Filter



- The circuit simplifies to the one shown above and the capacitances are given by

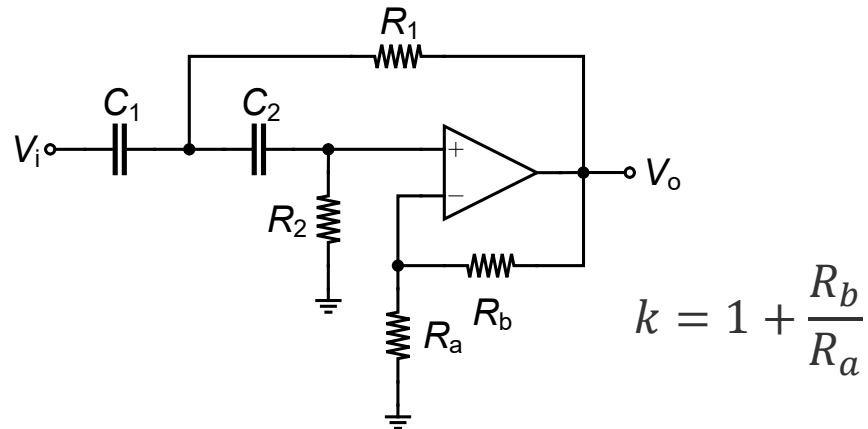
$$C_1 = \frac{2Q_p}{R\omega_p} \text{ and } C_2 = \frac{1}{2R\omega_p Q_p}$$

- The capacitance ratio can be calculated as

$$\frac{C_1}{C_2} = 4Q_p^2$$

- implying that for high Q values, the capacitors value spread can be undesirably high, presenting difficulties in the implementation
- This limits the usefulness of this design to **low Q filters**

# The Sallen-Key Single OPAMP Second-order HP Filter



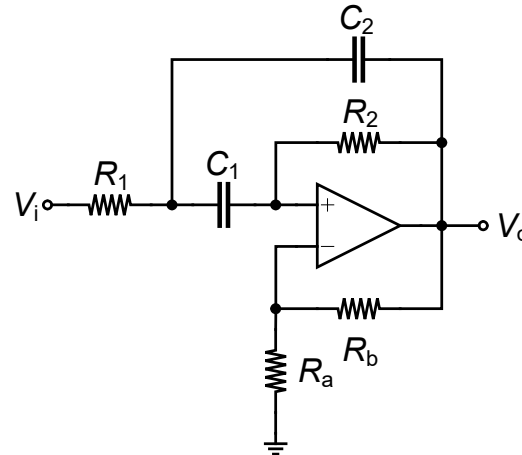
- Applying the LP-to-HP transformation we get the 2<sup>nd</sup>-order HP filter having a transfer function given by

$$T(s) \triangleq \frac{V_o}{V_i} = \frac{ks^2}{s^2 + \left( \frac{1}{R_2 C_2} + \frac{1}{R_2 C_1} + \frac{1-k}{R_1 C_1} \right) s + \frac{1}{R_1 R_2 C_1 C_2}} = \frac{ks^2}{s^2 + \frac{\omega_p}{Q_p} s + \omega_p^2}$$

- where  $k = 1 + R_b/R_a$  is the dc gain of the noninverting amplifier
- The corresponding design equations are given below

$$\omega_p = \frac{1}{\sqrt{R_1 R_2 C_1 C_2}} \text{ and } Q_p = \frac{\sqrt{R_1 R_2 C_1 C_2}}{R_1 (C_1 + C_2) + R_2 C_2 (1-k)}$$

# The Deliyannis Single OPAMP Second-order BP Filter



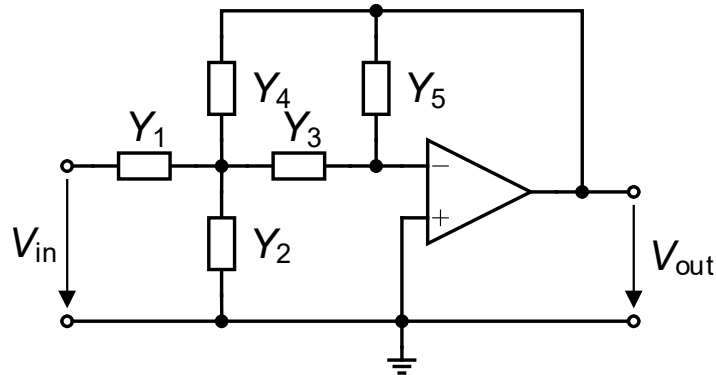
- A BP Sallen-Key 2<sup>nd</sup>-order filter is shown above with the following transfer function

$$T(s) \triangleq \frac{V_o}{V_i} = \frac{\frac{1+K}{R_1 C_2} s}{s^2 + \left( \frac{C_1 + C_2}{R_2 C_1 C_2} - \frac{K}{R_1 C_2} \right) s + \frac{1}{R_1 R_2 C_1 C_2}} = \frac{h s}{s^2 + \frac{\omega_p}{Q_p} s + \omega_p^2}$$

- where  $K = R_a/R_b$  and  $h = (1 + K)/(R_1 C_2)$
- The corresponding design equations are given below

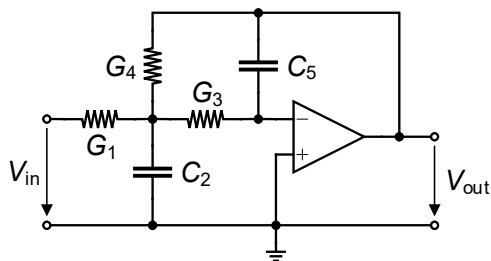
$$\omega_p = \sqrt{\frac{1}{R_1 R_2 C_1 C_2}} \text{ and } Q_p = \frac{\sqrt{R_1 R_2 C_1 C_2}}{R_1 (C_1 + C_2) - R_2 C_1 K}$$

# Multiple Feedback (MF) Single OPAMP Biquads



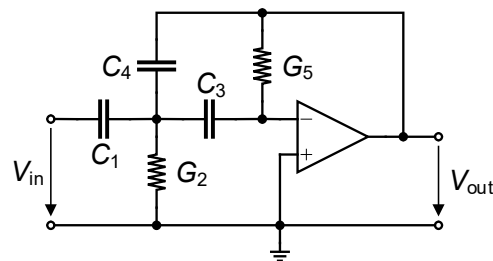
$$T(s) \triangleq \frac{V_{out}}{V_{in}} = \frac{-Y_1 Y_3}{Y_5(Y_1 + Y_2 + Y_3 + Y_4) + Y_3 Y_4}$$

Low-pass



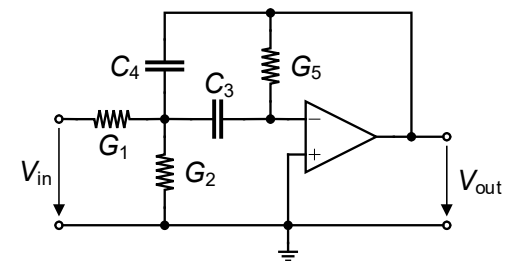
$$\frac{-G_1 G_3}{C_2 C_5 \cdot s^2 + C_5(G_1 + G_3 + G_4) \cdot s + G_3 G_4}$$

High-pass



$$\frac{-C_1 C_3 \cdot s^2}{C_3 C_4 \cdot s^2 + G_5(C_1 + C_3 + C_4) \cdot s + G_2 G_5}$$

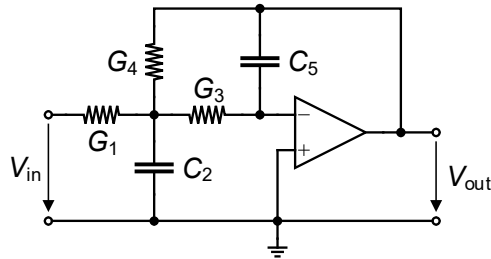
Band-pass



$$\frac{-G_1 C_3 \cdot s}{C_3 C_4 \cdot s^2 + G_5(C_3 + C_4) \cdot s + G_5(G_1 + G_2)}$$

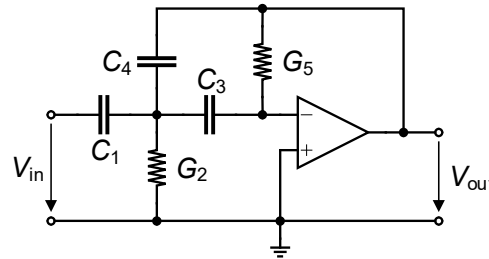
# Multiple Feedback (MF) Single OPAMP Biquads

Low-pass



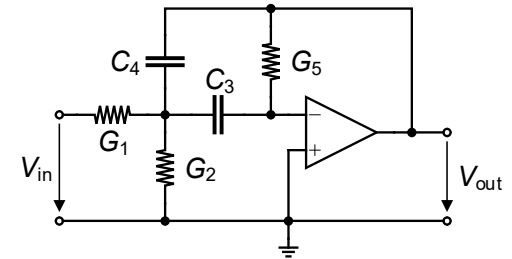
$$H(s) = \frac{K}{s^2 + \frac{\omega_p}{Q_p} \cdot s + \omega_p^2}$$

High-pass



$$H(s) = \frac{K \cdot s^2}{s^2 + \frac{\omega_p}{Q_p} \cdot s + \omega_p^2}$$

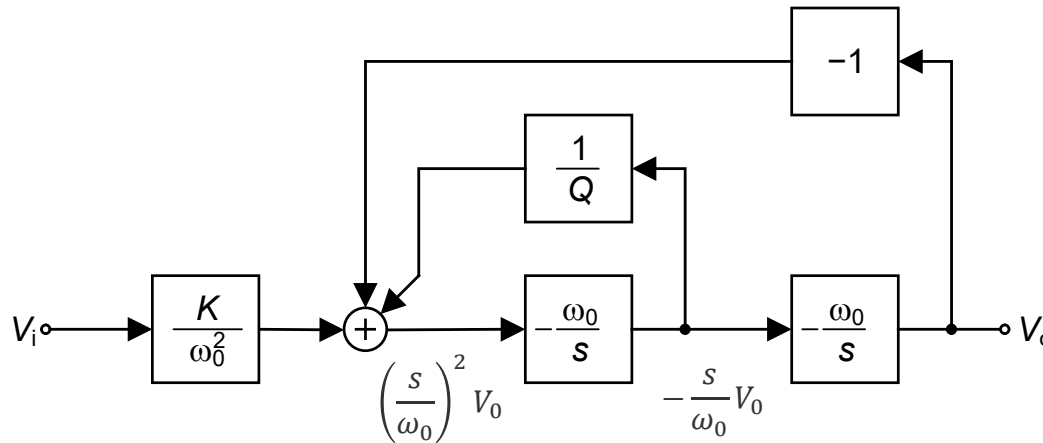
Band-pass



$$H(s) = \frac{K \cdot s}{s^2 + \frac{\omega_p}{Q_p} \cdot s + \omega_p^2}$$

Elements	Low-pass	High-pass	Band-pass
$Y_1$	$G_1 = K/\omega_p$	$C_1 = K$	$G_1 = K$
$Y_2$	$C_2 = \frac{Q_p(2\omega_p^2 + K)}{\omega_p^2}$	$G_2 = \omega_p(2 + K)Q_p$	$G_2 = 2\omega_p Q_p - K$
$Y_3$	$G_3 = \omega_p$	$C_3 = 1$	$C_3 = 1$
$Y_4$	$G_4 = G_3$	$C_4 = C_3$	$C_4 = C_3$
$Y_5$	$C_5 = \frac{\omega_p^2}{Q_p(2\omega_p^2 + K)}$	$G_5 = \frac{\omega_p}{Q_p(2 + K)}$	$G_5 = \frac{\omega_p}{2Q_p}$

# Block Diagram of a 2<sup>nd</sup>-order LP Transfer Function



- The 2<sup>nd</sup>-order LP transfer function

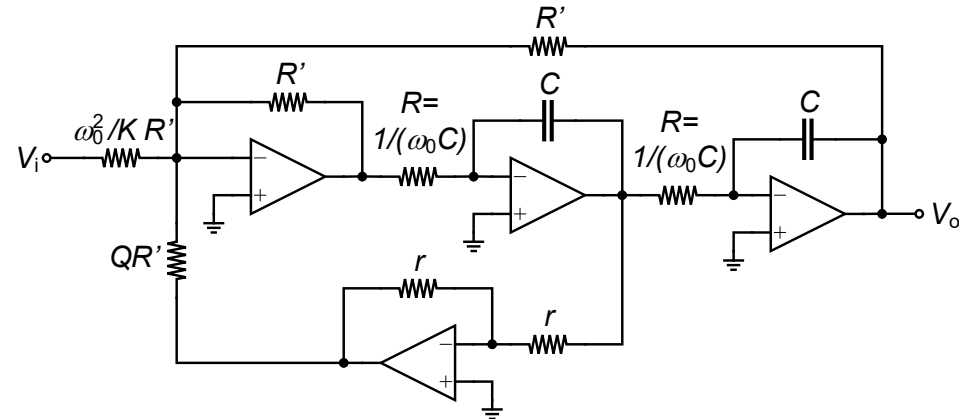
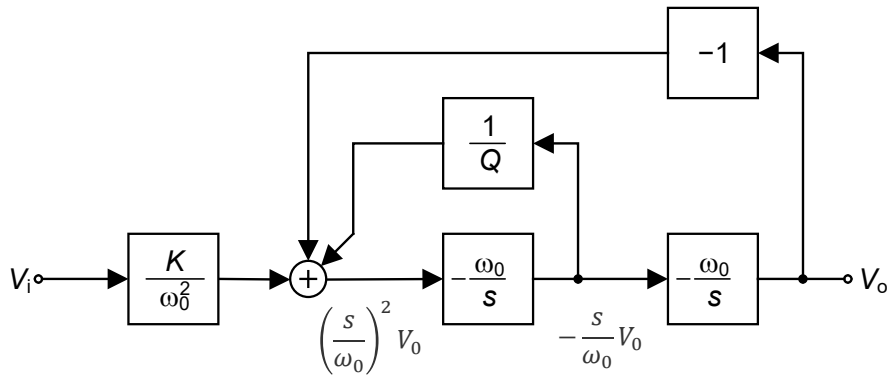
$$T_{LP}(s) \triangleq \frac{V_o}{V_i} = \frac{K}{s^2 + \frac{\omega_0}{Q}s + \omega_0^2} = \frac{\frac{K}{\omega_0^2}}{\left(\frac{s}{\omega_0}\right)^2 + \frac{1}{Q} \frac{s}{\omega_0} + 1}$$

- can be rewritten as

$$\left(\frac{s}{\omega_0}\right)^2 V_o = \frac{K}{\omega_0^2} V_i - \frac{1}{Q} \frac{s}{\omega_0} V_o - V_o$$

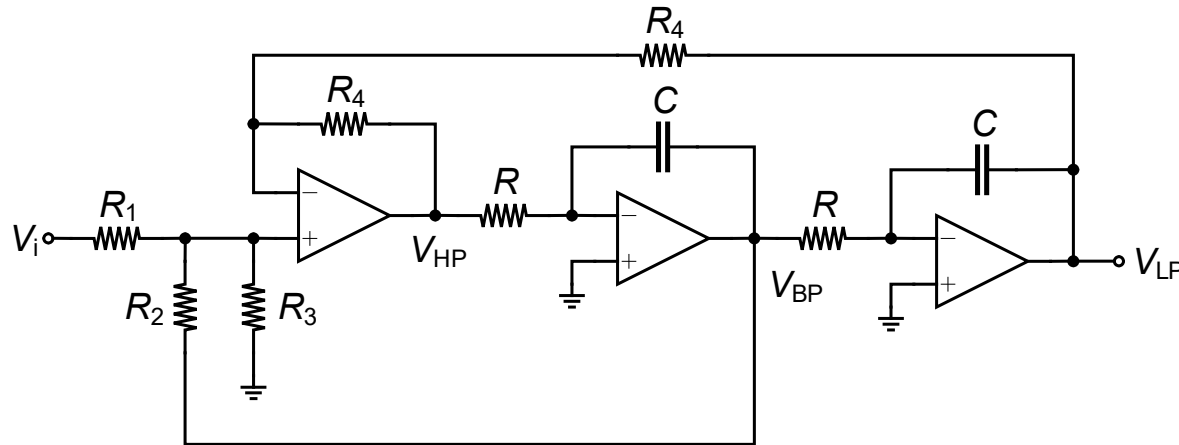
- which can be implemented with the block diagram shown above
- This block diagram can easily be implemented with OPAMPS

# From Block Diagram to Circuit Implementation



- Using OPAMPs to perform the summing and integration operations, we obtain the circuit shown on the right
- Straightforward analysis of this circuit shows that the function is realized with a minus sign
- To avoid this, and also the use of a fourth amplifier, we make use of the OPAMP difference circuit leading to the KHN (Kerwin, Huelsman, Newcomb) biquad shown in the next slide

# The Kerwin, Huelsman, Newcomb (KHN) Biquad



- The KHN offers the 3 different transfer functions LP, BP and HP

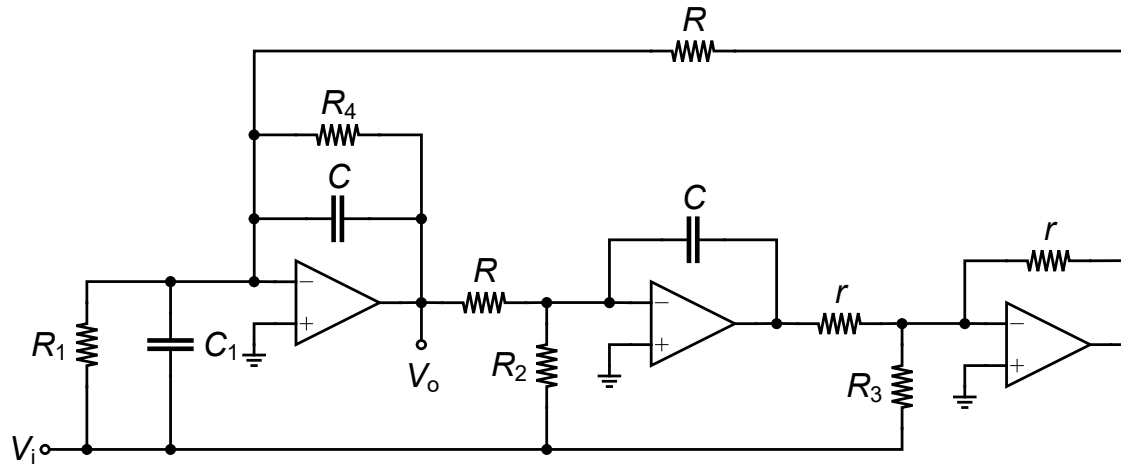
$$T_{LP}(s) \triangleq \frac{V_{LP}}{V_i} = K' \frac{\omega_0^2}{s^2 + \frac{\omega_0}{Q}s + \omega_0^2}$$

$$T_{BP}(s) \triangleq \frac{V_{BP}}{V_i} = K' \frac{\omega_0 s}{s^2 + \frac{\omega_0}{Q}s + \omega_0^2}$$

$$T_{HP}(s) \triangleq \frac{V_{HP}}{V_i} = K' \frac{s^2}{s^2 + \frac{\omega_0}{Q}s + \omega_0^2}$$

- with  $\omega_0 = \frac{1}{RC}$ ,  $K' = \frac{2R_2R_3}{R_1R_2 + R_1R_3 + R_2R_3}$  and  $Q = \frac{1}{2} \left( 1 + \frac{R_2}{R_1} + \frac{R_3}{R_1} \right)$

# The Generalized Tow-Thomas Biquad

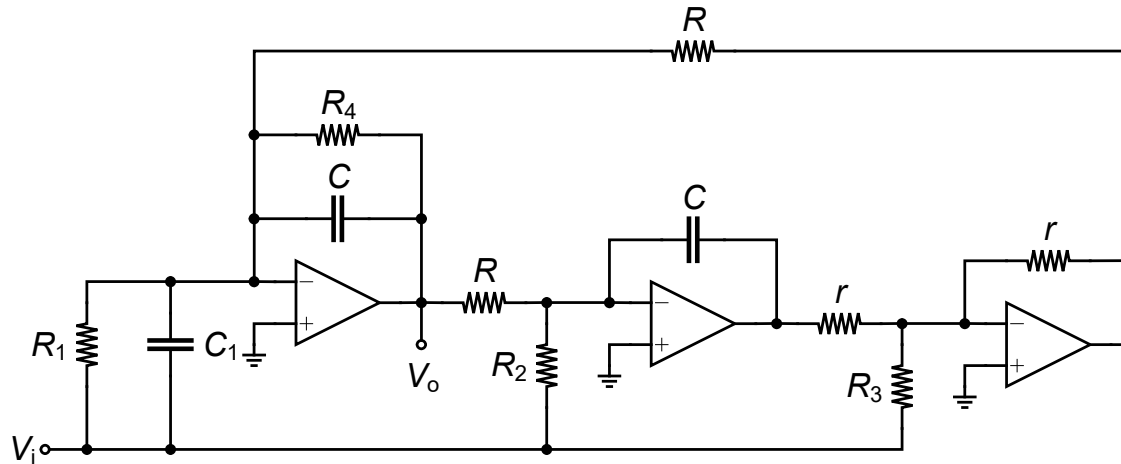


- A more versatile 3 OPAMPs biquad is the generalized Tow-Thomas shown above
- The transfer function is given by

$$T(s) \triangleq \frac{V_o}{V_i} = - \frac{\frac{C_1}{C} s^2 + \frac{1}{RC} \left( \frac{R}{R_1} - \frac{r}{R_3} \right) s + \frac{1}{RR_2C^2}}{s^2 + \frac{s}{R_4C} + \frac{1}{(RC)^2}}$$

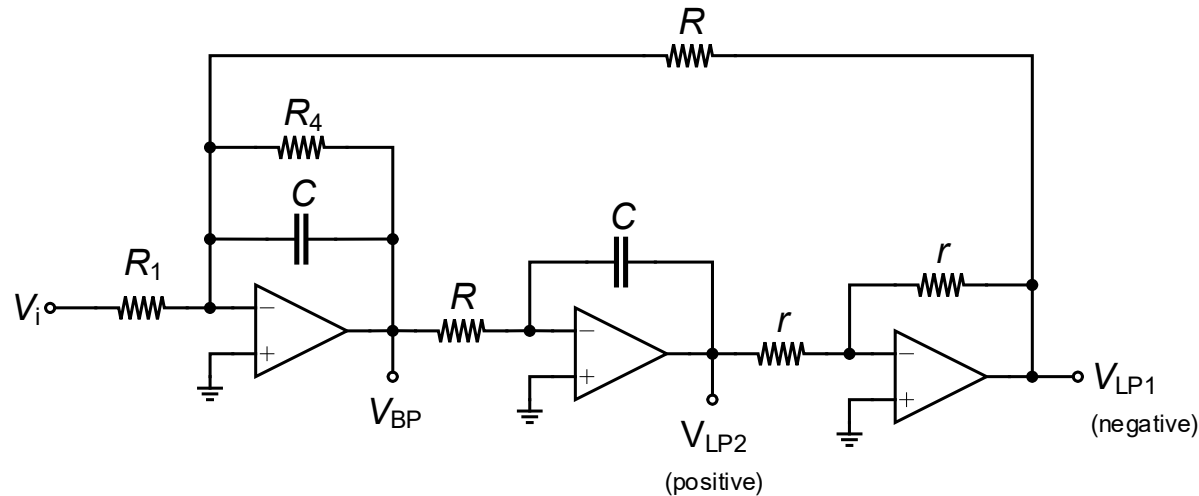
- Clearly, it is possible to obtain **any kind of second-order filter function** by a proper choice of the component values
- The choice is summarized in the table on the next slide

# The Generalized Tow-Thomas Biquad



Type	Conditions	Comments
LP	$C_1 = 0$ $R_1 = R_3 = \infty$	
BP	$C_1 = 0$ $R_1 = R_2 = \infty$	Positive sign
BP	$C_1 = 0$ $R_2 = R_3 = \infty$	Negative sign
HP	$C_1 = C$ $R_1 = R_2 = R_3 = \infty$	
Notch	$C_1 = C$ $R_1 = R_3 = \infty$	
Allpass	$C_1 = C$ $R_1 = \infty, r = R_3/Q$	

# The LP and BP Tow-Thomas Biquad



- The particular **LP** and **BP** cases of the Tow-Thomas biquad are shown above

$$T_{BP}(s) \triangleq \frac{V_{BP}}{V_i} = K \frac{\omega_0 s}{s^2 + \frac{\omega_0}{Q}s + \omega_0^2} \quad \text{and} \quad T_{LP}(s) \triangleq \frac{V_{LP1}}{V_i} = \frac{K}{s^2 + \frac{\omega_0}{Q}s + \omega_0^2}$$

- Where  $\omega_0 = \frac{1}{RC}$ ,  $Q = \frac{R_4}{R}$  and  $K = -\frac{R}{R_1}$
- We see that  $R_4$  sets the Q-factor **independently** of the center frequency  $\omega_0$  and  $R_1$  sets the gain in the passband

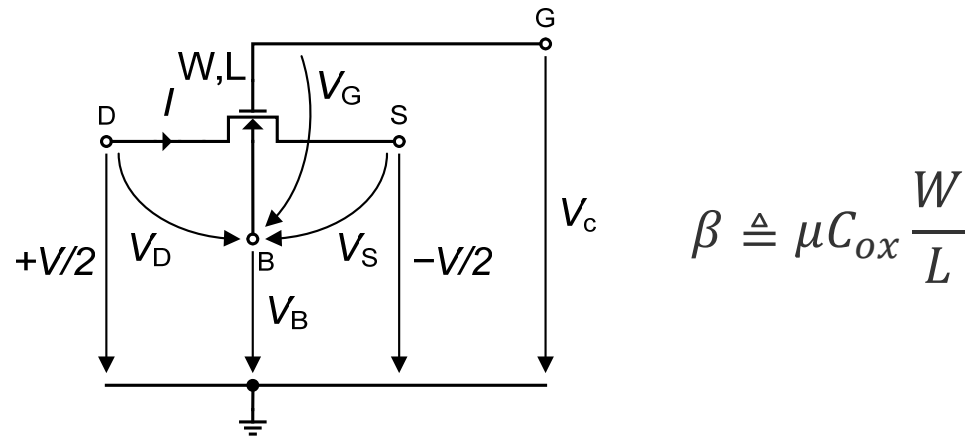
# Outline

- Introduction
- RC-active filters
- **MOSFET-C filters**
- $G_m$ -C filters
- Source-follower CTFs
- Noise in CTFs
- Automatic tuning

# MOSFET-C Filters – Linear MOSFET Resistors

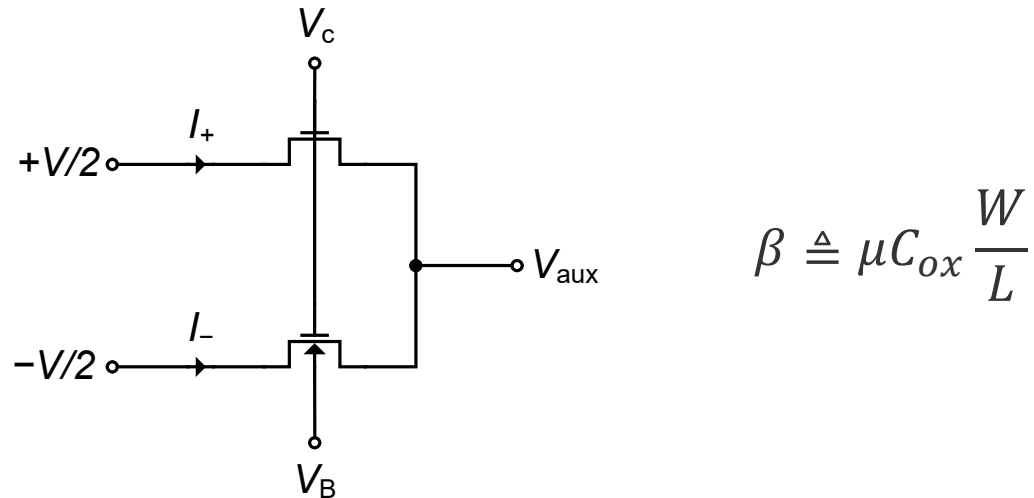
- MOSFET-C filters are derived from **active-RC filter** where the resistors are replaced by one or several MOS transistors
- MOSFET-C hence require linear resistors made of one or several MOS transistors usually operated in their linear range and in SI
- Linear operation is achieved by **cancellation of even-order nonlinearities** using balanced signals with differential circuits
- Remaining odd-order terms are usually very small
- Several basic circuit principle for the implementation of linear MOSFET resistors will be examined:
  - ▶ **Single** device with balanced source and drain voltages
  - ▶ **Two** devices with balanced drains and common source
  - ▶ **Four** devices (bridge)

# Linear MOSFET Resistors – Circuit Principle 1



- Balanced operation of a single MOST biased in linear region and in SI
- Drain current:  $I = n\beta \left( V_P - \frac{V_D + V_S}{2} \right) (V_D - V_S)$  for  $V_S, V_D < V_P \cong \frac{V_G - V_{T0}}{n}$
- Linear operation if  $V_D - V_S = V$  and  $V_D + V_S = -2V_B$  resulting in
 
$$I = n\beta(V_P + V_B) \cdot V = G \cdot V = V/R$$
- with  $G = n\beta(V_P + V_B) \cong \beta(V_G - V_{T0} + nV_B) = \beta(V_C - V_{T0} + (n - 1)V_B)$
- provided  $|V| < \max \left\{ 2V_B; 2 \frac{V_C - V_{T0} + (n-1)V_B}{n} \right\}$
- Nonlinearity cancellation relies on **precise voltage balancing**

## Linear MOSFET Resistors – Circuit Principle 2



- Two MOSFETs in differential configuration biased in the linear region and in SI and with balanced input

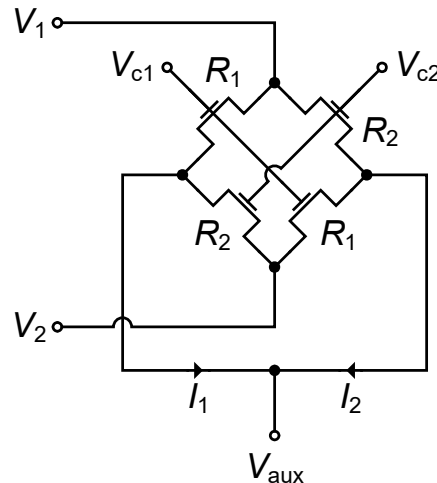
$$\Delta I \triangleq I_+ - I_- = n\beta(V_P + V_B) \cdot V = G \cdot V = V/R$$

- with  $G = n\beta(V_P + V_B) \cong \beta(V_G - V_{T0} + nV_B) = \beta(V_C - V_{T0} + (n - 1)V_B)$
- independently of the value of  $V_{aux}$  provided

$$|V| < \max \left\{ 2V_B; 2 \frac{V_C - V_{T0} + (n-1)V_B}{n} \right\} \text{ and } V_B < V_{aux} < \frac{V_C - V_{T0} + (n-1)V_B}{n}$$

- Nonlinearity cancellation relies on proper **voltage balancing** and **device matching**

## Linear MOSFET Resistors – Circuit Principle 3



- **Four** MOSFETs in bridge configuration with **all transistors identical** and biased in the linear region and in SI
- Input voltage includes a common mode component  $V_{ic}$  in addition to the differential term  $V$  with  $V_1 = V_{ic} + V/2$  and  $V_2 = V_{ic} - V/2$  resulting in
 
$$\Delta I \triangleq I_2 - I_1 = \beta(V_{c1} - V_{c2}) \cdot V = G \cdot V = V/R$$
- with  $G = G_1 - G_2 = \beta(V_{c1} - V_{c2})$  where  $G_i = 1/R_i$  for  $i = 1,2$
- Does not depend on input common mode voltage  $V_{ic}$  neither on threshold voltage
- Depends on the difference between the control voltages  $V_{c1} - V_{c2}$

# Linear MOSFET Resistors – Circuit Principle 3

## Pros

- + Both even and odd harmonics are cancelled (assuming perfect device matching and constant mobility)
- + Input signals  $V_1$  and  $V_2$  do not need to be fully balanced (they can have a non zero common mode term)
- + Resistance  $R$  is controlled by a differential voltage  $V_{c1} - V_{c2}$ 
  - +  $R$  can be negative as well as positive
  - +  $R$  is insensitive to  $V_{T0}$  and common mode noise

## Cons

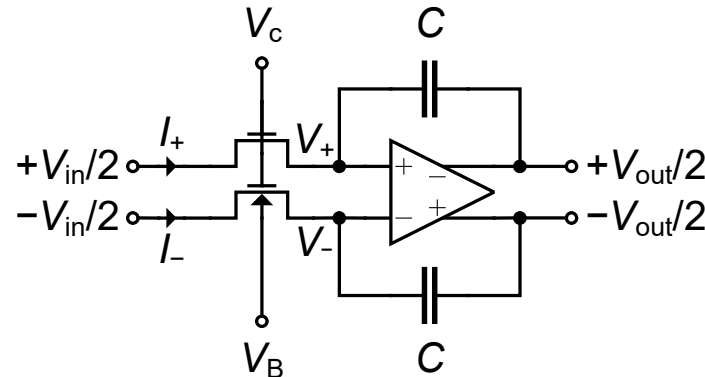
- Complexity, requires 4 matched devices and two control voltages
- Highly sensitive to mismatches ( $\Delta\beta$  and  $\Delta V_T$ ) for  $R \gg R_1, R_2$  (i.e.  $V_{c1}$  close to  $V_{c2}$ )
- Higher noise than for circuits 1 and 2  
excess noise factor  $\gamma$  given by

$$\gamma \triangleq R \cdot G_n = 1 + \frac{2R}{R_2}$$

where  $G_n$  is the noise conductance of the resistances

- This is higher compared to  $\gamma = 1$  for circuits 1 and 2
- Example with  $R = R_2$  ( $R_1 = R/2$ )  
 $\gamma = 3$

# MOSFET-C Filters – Basic Fully Differential Integrator



- Combination of a linear MOSFET resistor using the circuit principle 2 and a fully differential OPAMP with a balanced output (incl. an output common-mode feedback)
- Assuming OPAMP with infinite input impedance and matched capacitances

$$+\frac{V_{out}}{2} = V_+ - \frac{1}{C} \int_{-\infty}^t I_+(\tau) d\tau \quad \text{and} \quad -\frac{V_{out}}{2} = V_- + \frac{1}{C} \int_{-\infty}^t I_-(\tau) d\tau$$

- Assuming infinite differential gain  $\rightarrow V_+ = V_-$

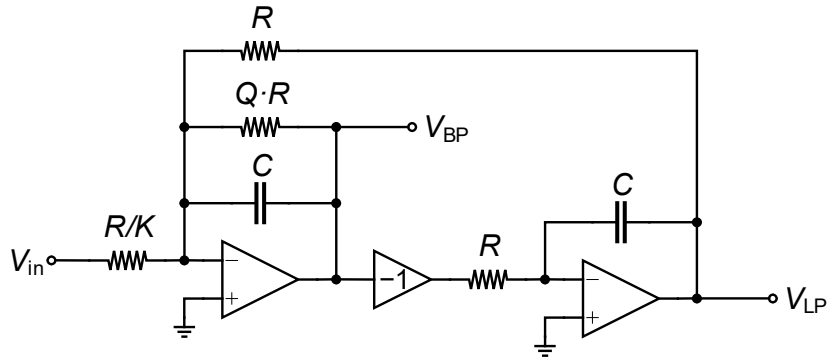
$$V_{out} = -\frac{1}{C} \int_{-\infty}^t (I_+(\tau) - I_-(\tau)) d\tau = -\frac{1}{RC} \int_{-\infty}^t V_{in}(\tau) d\tau$$

- where  $R^{-1} = G = \beta(V_C - V_{T0} + (n - 1)V_B)$
- Note that fully differential OPAMP requires a common-mode feedback (CMFB) circuit to set the output common mode voltage

# MOSFET-C Filters – OPAMP Requirements

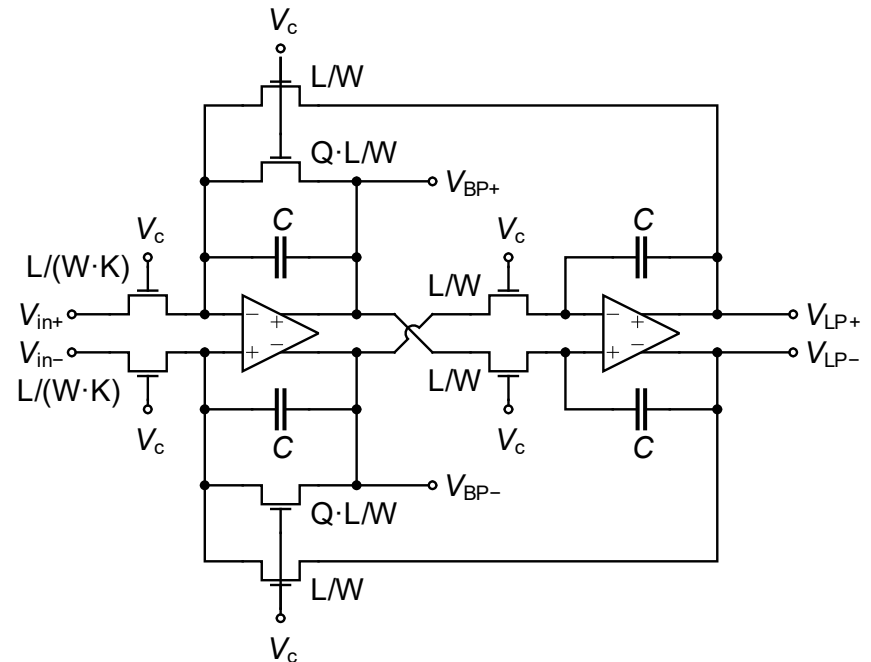
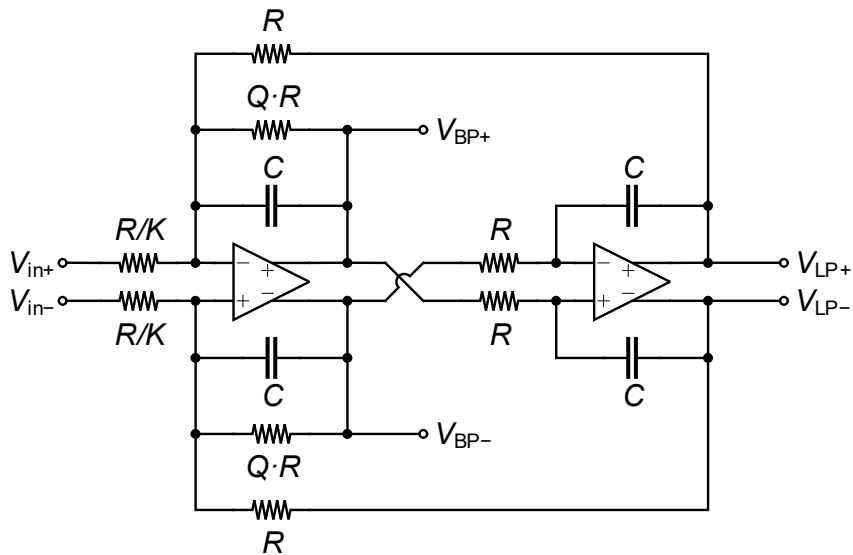
- Low output impedance ( $R_{out} \ll R_{MOSFET}$ )
- High gain-bandwidth product in order to achieve:
  - ▶ small errors in the filter frequency response
  - ▶ accurate nonlinearity cancellation
- Fast and accurate output CMFB to maintain precise voltage balancing over the entire frequency range where nonlinearity cancellation are important
- Modest input common-mode range and rejection capabilities (input common-mode voltage is an even nonlinear function of the input signal)

# MOSFET-C Filters – The Tow-Thomas Biquad

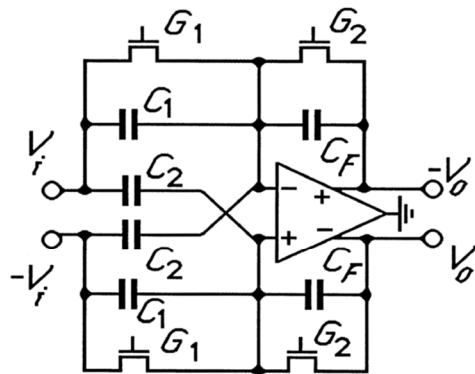


$$H_{BP}(s) \triangleq \frac{V_{BP}}{V_{in}} = K \frac{\omega_0 s}{s^2 + \frac{\omega_0}{Q} s + \omega_0^2}$$

$$H_{LP}(s) \triangleq \frac{V_{LP}}{V_{in}} = \frac{K}{s^2 + \frac{\omega_0}{Q} s + \omega_0^2}$$

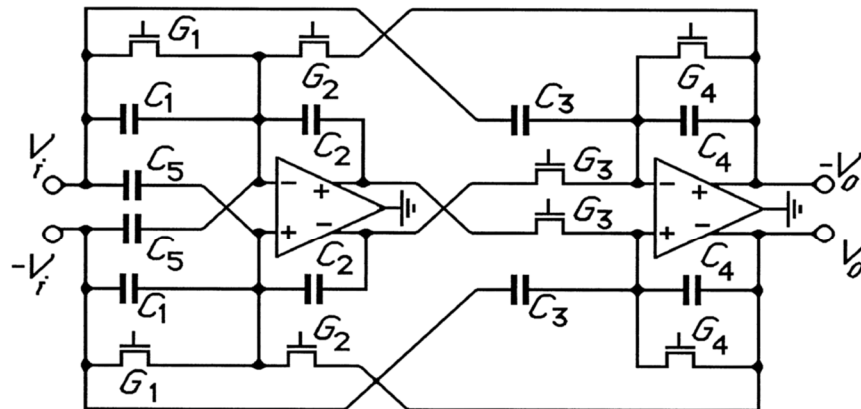


# Generic 1<sup>st</sup>- and 2<sup>nd</sup>-order MOSFET-C Section



(a)

$$H_1(s) = \frac{s(C_1 - C_2) + G_1}{sC_F + G_2}$$



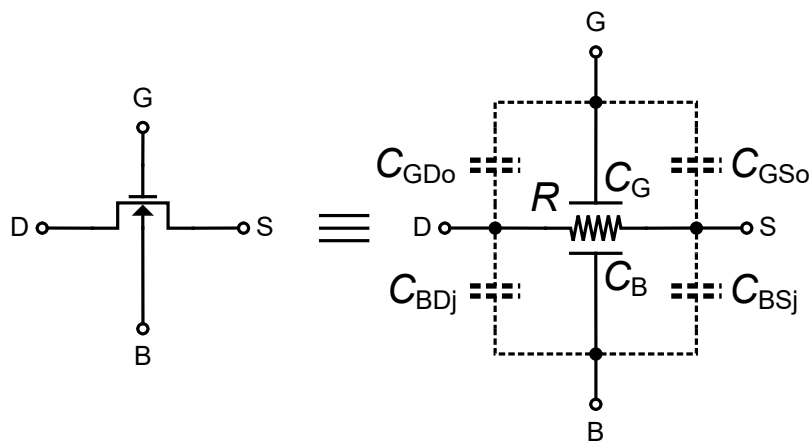
(b)

$$H_2(s) = \frac{s^2 C_2 C_3 + s(C_1 - C_5)G_3 + G_1 G_3}{s^2 C_2 C_4 + sC_2 G_4 + G_2 G_3}$$

Function	Choice of element
Bandpass	$G_1 = C_3 = 0$ ; $C_5 = 0$ if non-inverting, $C_1 = 0$ if inverting
Low-pass	$C_1 = C_3 = C_5 = 0$
High-pass	$C_1 = C_5 = G_1 = 0$
Notch	$C_1 = C_5$
All-pass	$(C_1 - C_5) \cdot G_3 = -C_2 \cdot G_4$

# MOSFET-C Filters – Non-Ideal Effects

- Nonlinear distortions
  - ▶ Device mismatch and signal imbalance → imperfect even-order distortions cancellation
  - ▶ Departure from simple square-law model (due to mobility variation, moderate inversion effects, etc...) → odd-order distortions
- Errors in the frequency response
  - ▶ Extra phase shift in the integrators due to:
    - ▶ finite OPAMP bandwidth
    - ▶ distributed gate-to-channel and channel-to-bulk capacitances



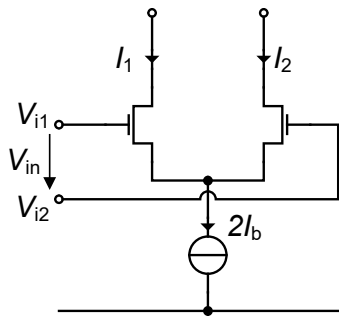
1<sup>st</sup>-order modeling of distributed RC effect by a time constant in the V/I transfer function

$$\begin{aligned} \tau_{RC} &= \frac{1}{6} \cdot R \cdot (C_G + C_B) = \frac{1}{6} \cdot R \cdot n \cdot W \cdot L \cdot C_{ox} = \\ &= \frac{1}{6} \cdot \frac{L^2}{\mu \cdot (V_P + V_B)} \cong \frac{1}{6} \cdot \frac{n \cdot L^2}{\mu \cdot (V_G - V_{T0} + nV_B)} \end{aligned}$$

# Outline

- Introduction
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- **$G_m$ -C filters**
- Source-follower CTFs
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- Automatic tuning

# Differential Pair in Weak Inversion

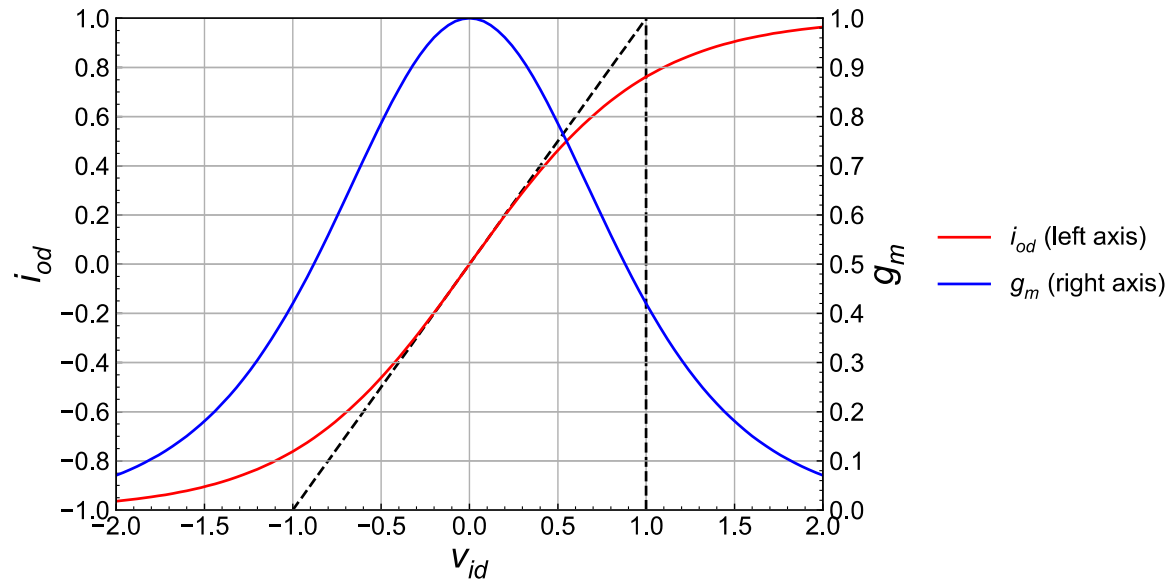


$$I_{od} \triangleq I_1 - I_2$$

$$2I_b = I_1 + I_2$$

$$V_{id} \triangleq V_{i1} - V_{i2}$$

$$V_{ic} \triangleq \frac{V_{i1} + V_{i2}}{2}$$



- In **weak inversion**, the normalized differential output current is given by

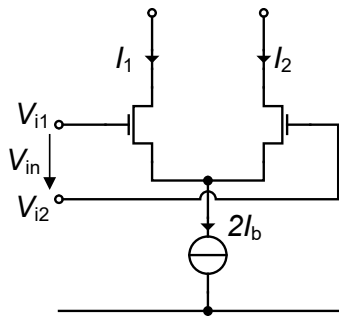
$$i_{od} \triangleq \frac{I_{od}}{2I_b} = \tanh(v_{id}) \text{ with } v_{id} \triangleq \frac{V_{id}}{2nU_T}$$

- and the normalized transconductance by

$$g_m \triangleq \frac{G_m}{G_{m0}} = 1 - \tanh^2(v_{id}) \text{ with } G_{m0} \triangleq G_m(0) = \frac{I_b}{nU_T}$$

- Although it offers the **highest current efficiency**  $G_{m0}/(2I_b)$ , it has the **smallest linear range** ( $\cong 4nU_T \cong 155 \text{ mV}$ )

# Differential Pair in Strong Inversion

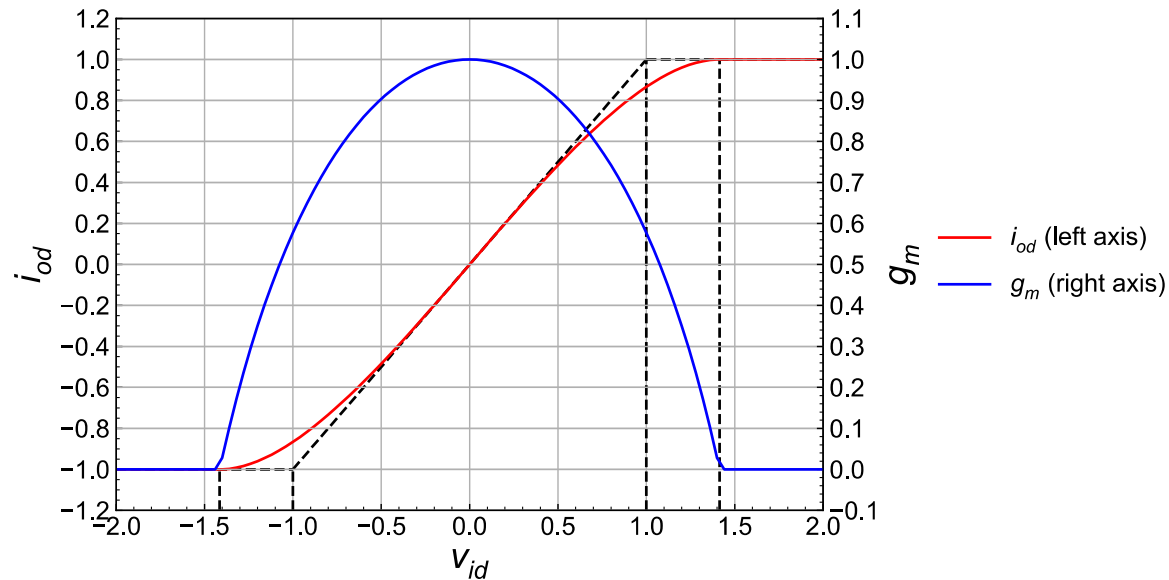


$$I_{od} \triangleq I_1 - I_2$$

$$2I_b = I_1 + I_2$$

$$V_{id} \triangleq V_{i1} - V_{i2}$$

$$V_{ic} \triangleq \frac{V_{i1} + V_{i2}}{2}$$



- In **strong inversion**, the normalized differential output current is given by

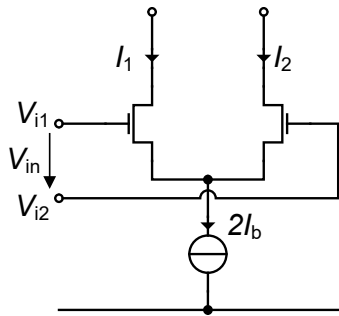
$$i_{od} \triangleq \frac{I_{od}}{2I_b} = v_{id} \cdot \sqrt{1 - \left(\frac{v_{id}}{2}\right)^2} \text{ for } |v_{id}| \leq \sqrt{2} \text{ with } v_{id} \triangleq \frac{V_{id}}{nV_{DSsat}} = \frac{V_{id}}{n(V_p - V_S)} = \frac{V_{id}}{V_G - V_{T0} - nV_S}$$

- and the normalized transconductance by

$$g_m \triangleq \frac{G_m}{G_{m0}} = \frac{2 - v_{id}^2}{\sqrt{4 - v_{id}^2}} \text{ with } G_{m0} \triangleq G_m(0) = \sqrt{\frac{2\beta I_b}{n}} = \frac{2I_b}{nV_{DSsat}} = \frac{2I_b}{n(V_p - V_S)} = \frac{2I_b}{V_G - V_{T0} - nV_S}$$

- The linear range ( $\cong V_G - V_{T0} - nV_S$ ) can be extended by increasing the overdrive voltage  $V_G - V_{T0}$  at the cost of a lower current efficiency

# Differential Pair in All Regions of Inversion

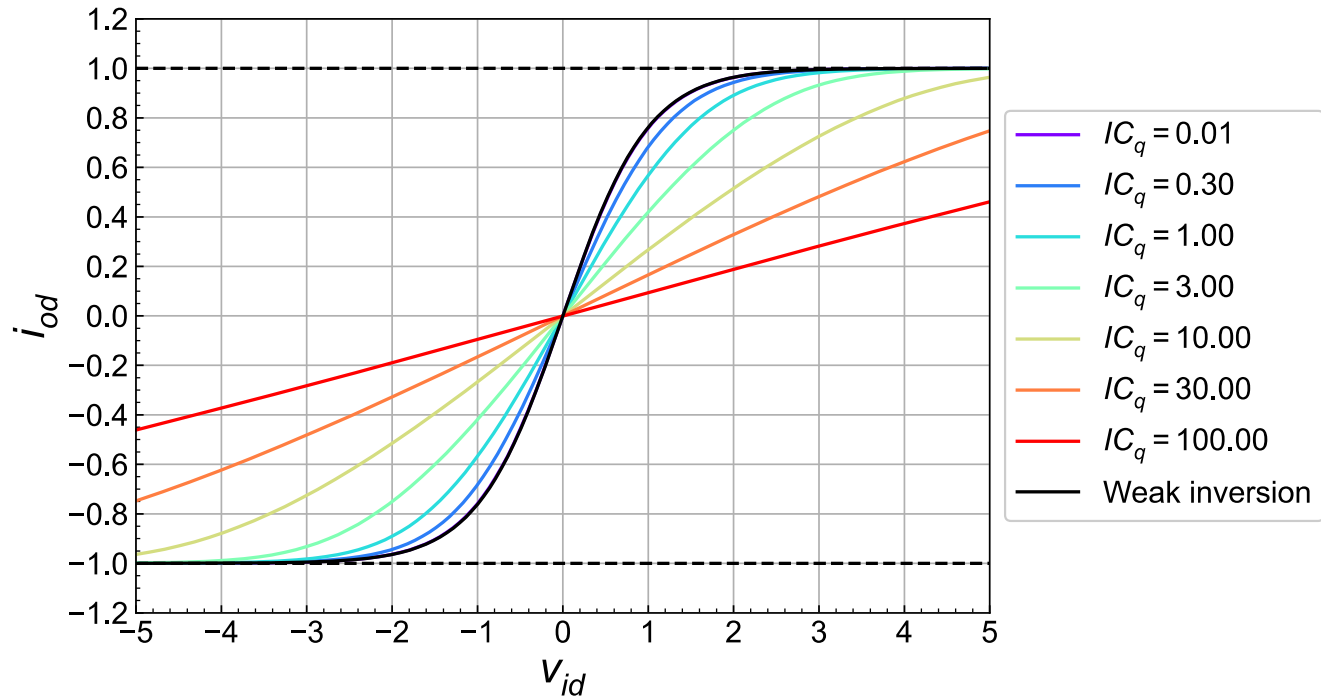


$$I_{od} \triangleq I_1 - I_2$$

$$2I_b = I_1 + I_2$$

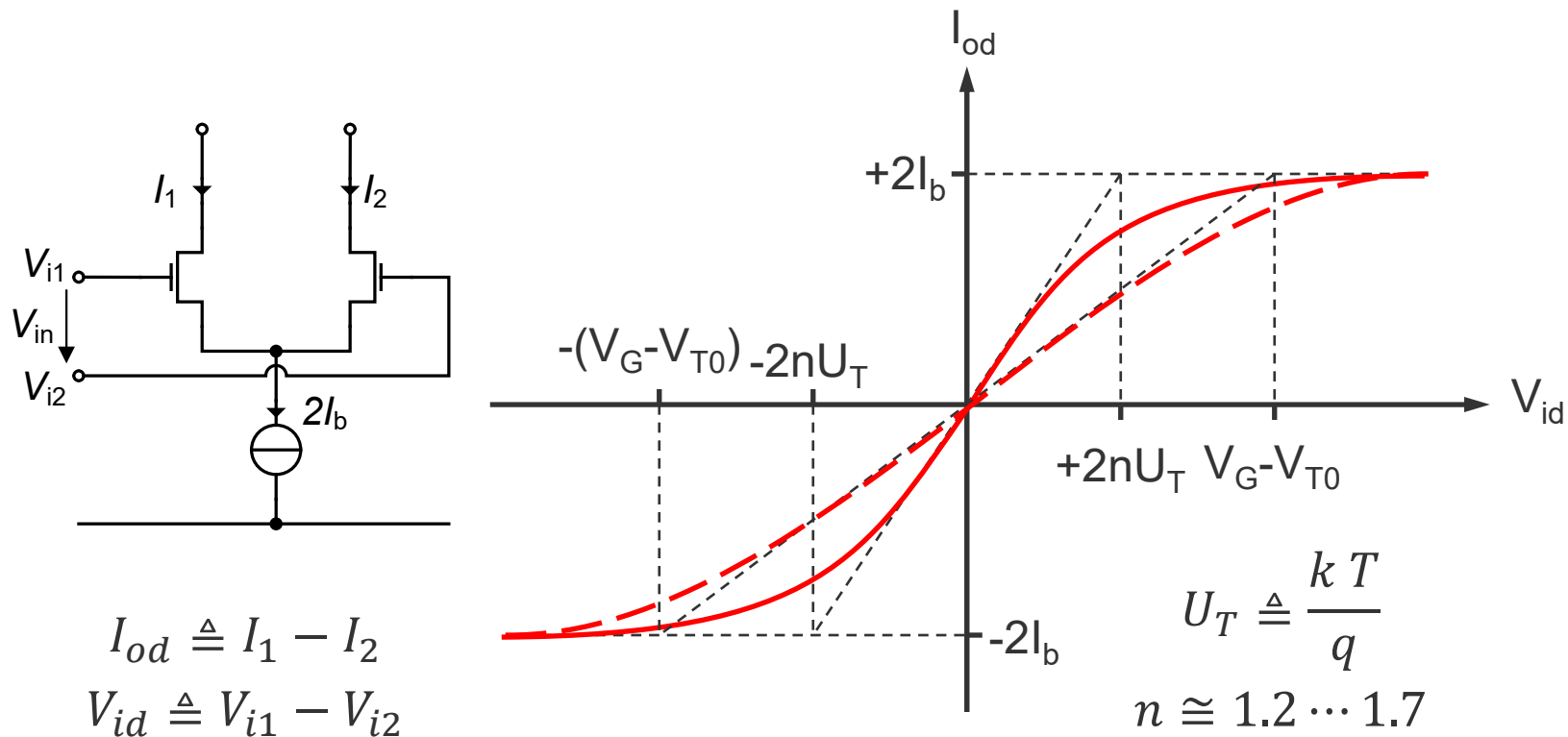
$$V_{id} \triangleq V_{i1} - V_{i2}$$

$$V_{ic} \triangleq \frac{V_{i1} + V_{i2}}{2}$$



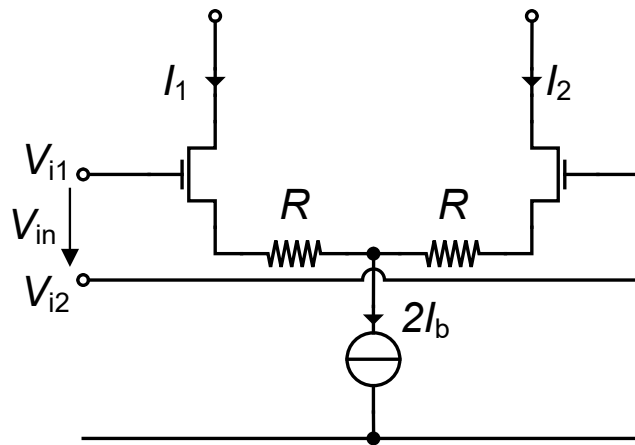
- The normalized differential current  $i_{od} \triangleq I_{od}/(2I_b)$  can be calculated versus the differential input voltage  $v_{id} \triangleq V_{id}/(2nU_T)$  in all regions of inversion defined by the quiescent inversion coefficient  $IC_q = I_b/I_{spec}$
- The above plot illustrates how moving to strong inversion extends the linear range

# Linearization Based on the Overdrive Voltage $V_G - V_{T0}$



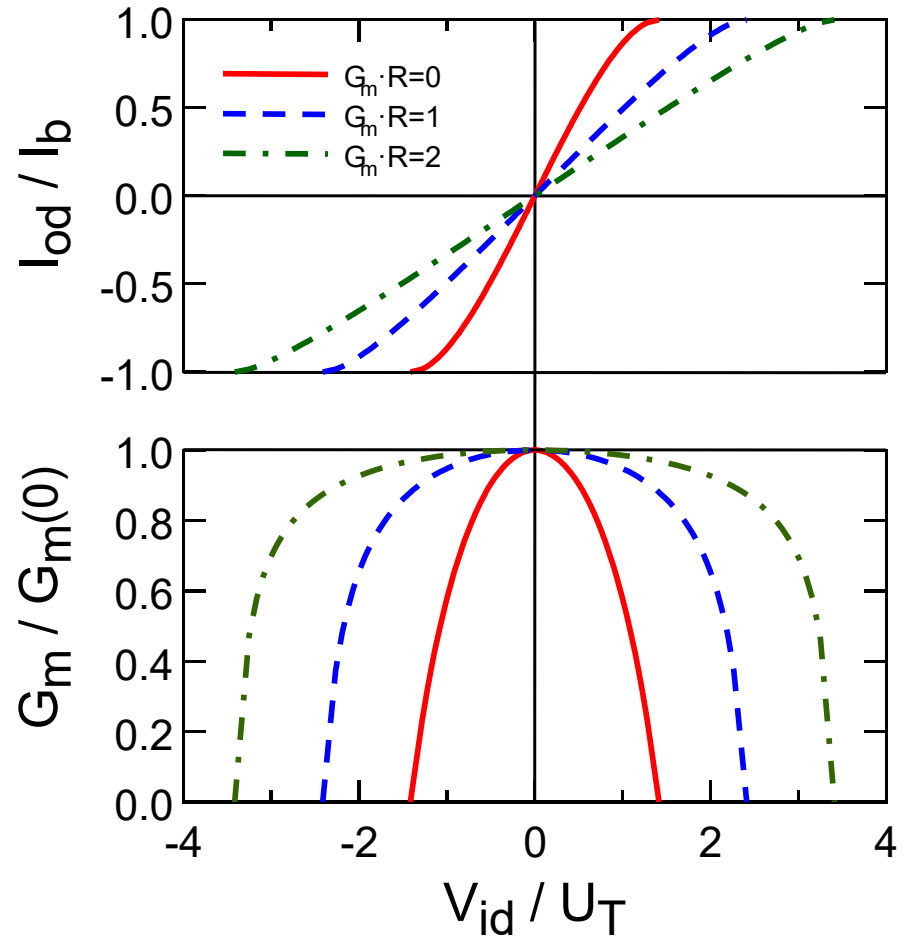
- Basically does not change the shape of the I-V characteristic, but scales the input voltage according to  $V_G - V_{T0}$

# Differential Pair Degenerated with Resistor



$$I_{od} \triangleq I_1 - I_2$$

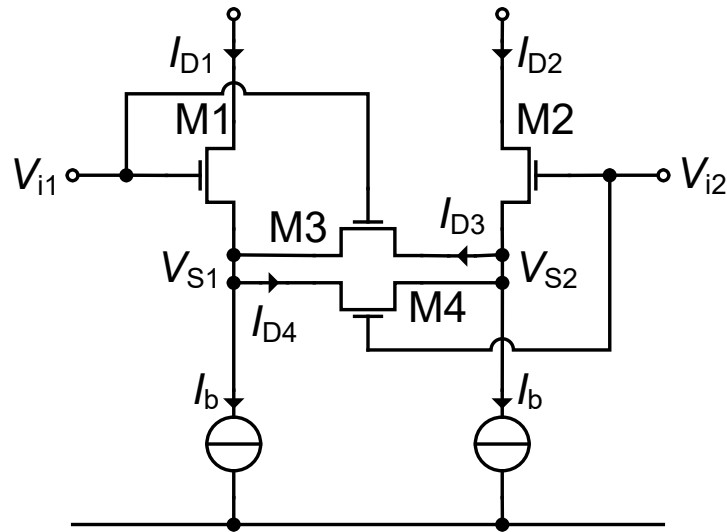
$$V_{id} \triangleq V_{i1} - V_{i2}$$



- Not appropriate for low-voltage



# The Krummenacher Differential Pair – Principle



$$I_{od} \triangleq I_{D1} - I_{D2}$$

$$V_{id} \triangleq V_{i1} - V_{i2}$$

- Degenerating resistor implemented with two MOSFETs operating in the linear region and controlled by the inputs
- M1 and M2 in saturation
- For  $V_{id}$  close to 0, M3 and M4 are in the linear region
- When  $V_{id} > 0$  becomes larger, M4 enters in saturation whereas M3 remains in the linear region

# The Krummenacher Differential Pair – Strong Inversion

- M1 and M2 in saturation and M3 and M4 in the linear region for  $v_{id} < v_k$

$$i_{od} = v_{id} \cdot \sqrt{1 - \frac{v_{id}^2}{4}} \text{ for } v_{id} < v_k \text{ where } v_k \triangleq \sqrt{\frac{2a^2 + 2a + 1}{2a^4 + \frac{1}{2}}} \text{ with } a \triangleq 1 + \frac{\beta_1}{4\beta_3}$$

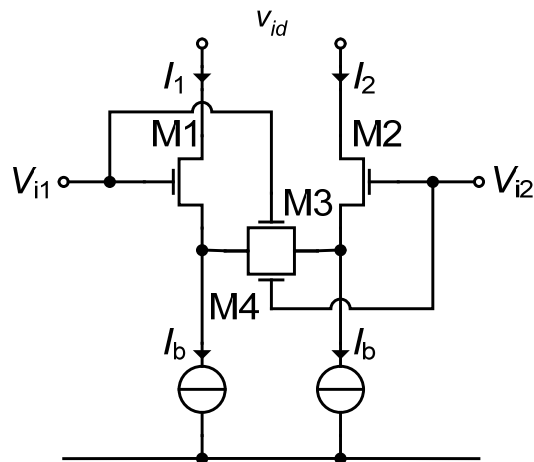
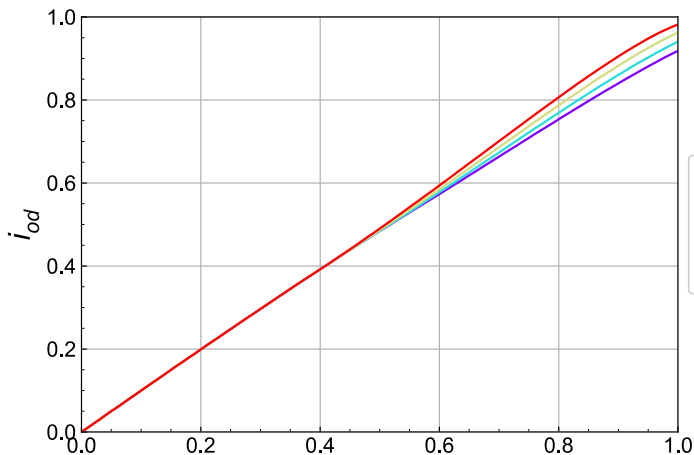
- where  $i_{od} \triangleq \frac{I_{od}}{2I_b}$ ,  $v_{id} \triangleq \frac{G_{m0}}{2I_b} \cdot V_{id}$ ,  $G_{m0} \triangleq \frac{G_{m1}}{1 + \frac{\beta_1}{4\beta_3}}$ ,  $G_{m1} = \sqrt{\frac{2\beta_1 I_b}{n}}$

- M1, M2 and M4 in saturation, M3 in the linear region for  $v_{id} \geq v_k$

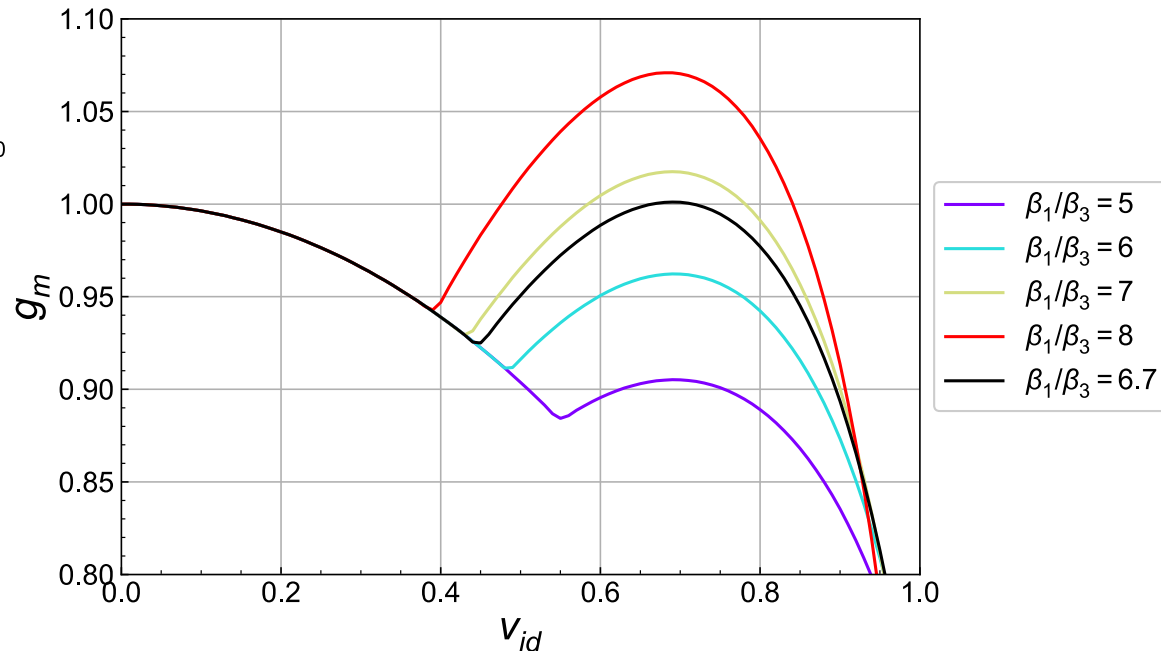
$$i_{od} = \frac{1}{b} \left[ 1 + (av_{id})^2 \left(1 - \frac{2}{b}\right) + 2av_{id} \sqrt{1 - \frac{1 + (av_{id})^2 \left(1 - \frac{1}{b}\right)}{b}} \right] \text{ with } b \triangleq 3 + \frac{\beta_1}{\beta_3}$$

- The transconductance  $G_{m0}$  defined at  $V_{id} = 0$  is  $1 + \beta_1/(4\beta_3)$  times smaller than the transconductance  $G_{m1}$  of the normal differential pair

# Krummenacher Differential Pair – Strong Inversion

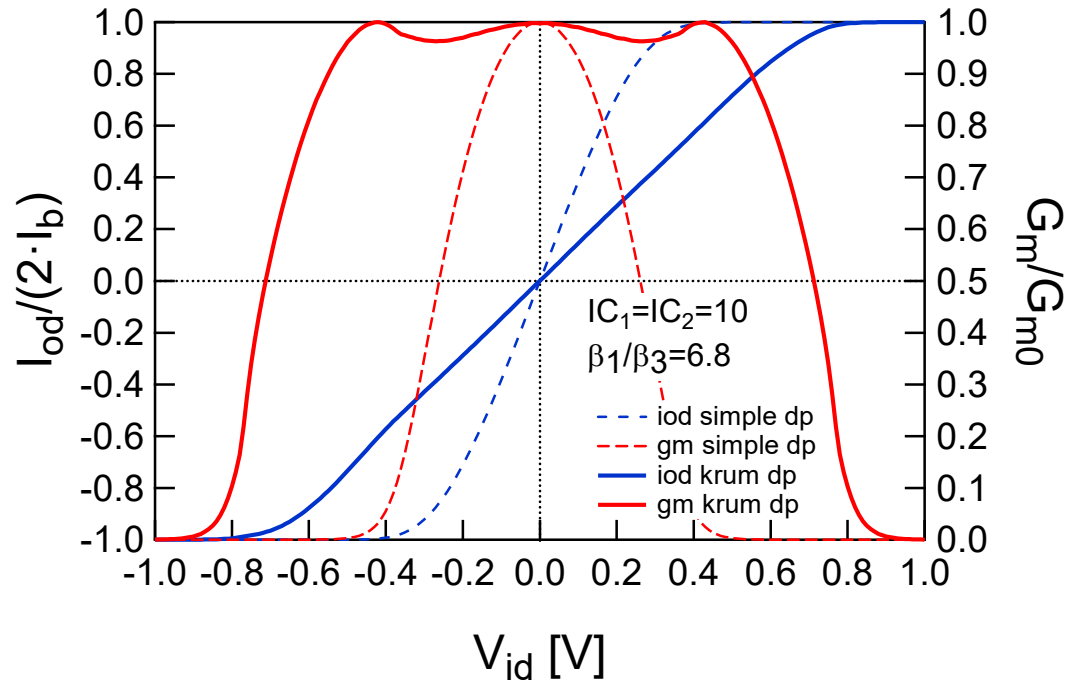
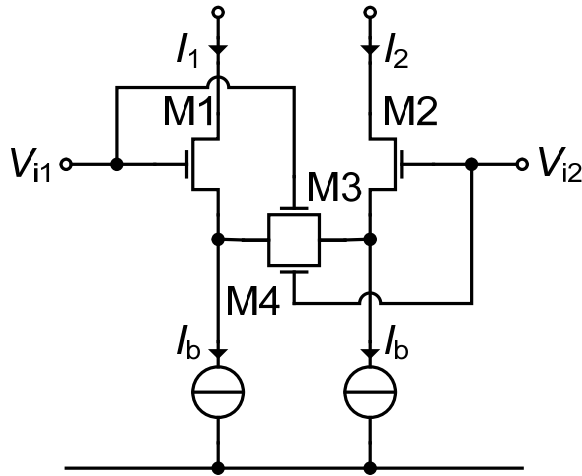


$$g_m = \frac{di_{od}}{dv_{id}} = \frac{G_m}{G_{m0}}$$



- Residual  $G_m$  ripple is minimum for  $\beta_1/\beta_3 \approx 6.7$
- Linear range extended by  $\sim 2x$  without degradation of the current efficiency compared to normal differential pair with the same bias

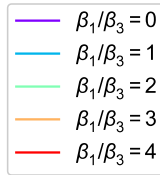
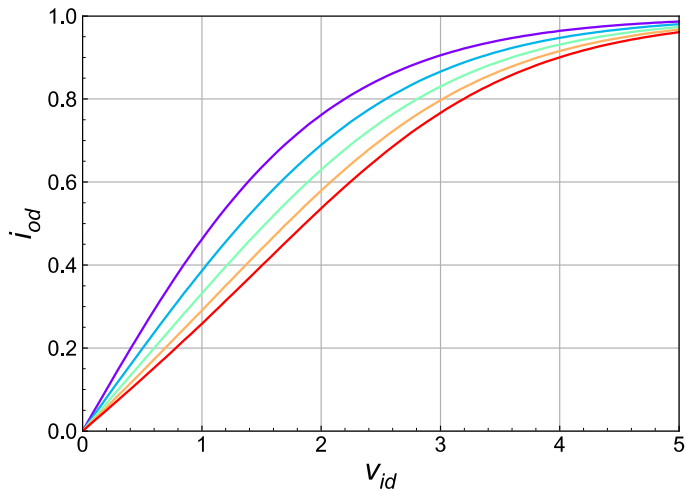
# The Krummenacher Differential Pair – Strong Inversion



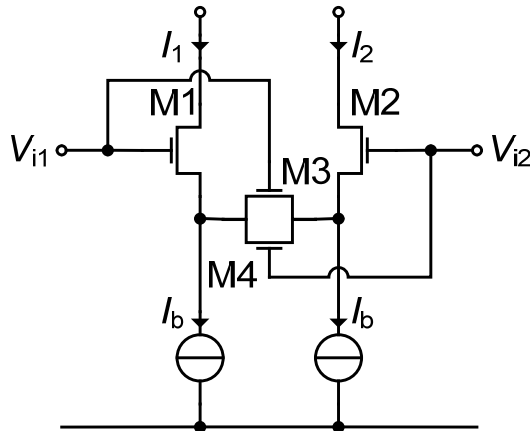
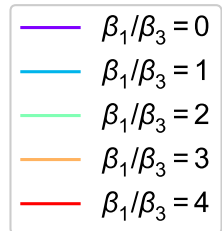
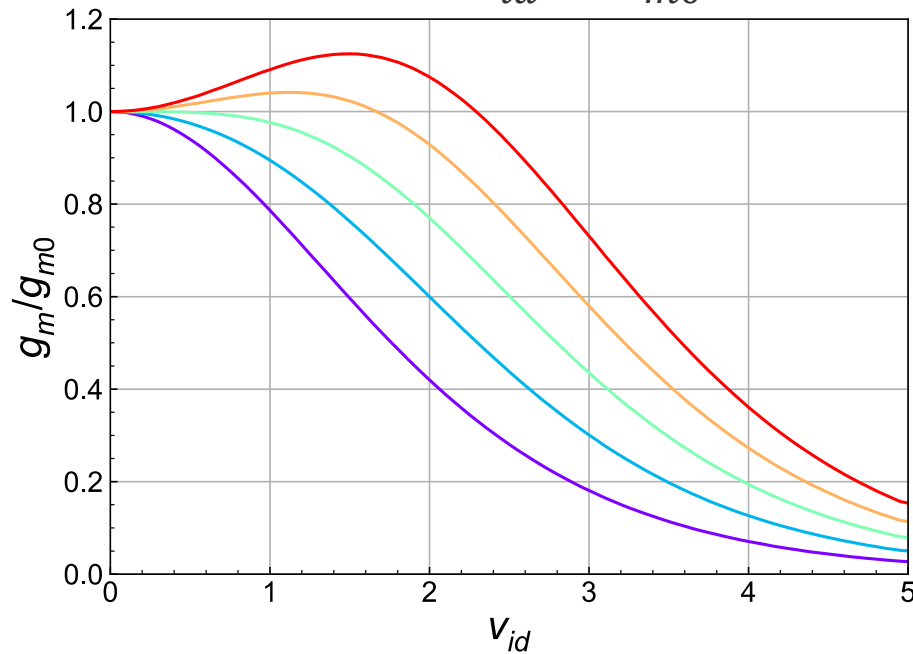
- Simulation with full EKV model for  $IC = 10$
- Residual  $G_m$  ripple is minimum for  $\beta_1/\beta_3 \approx 6.8$
- High current efficiency since no additional current branch
- Good noise performance



# Krummenacher Differential Pair – Weak Inversion

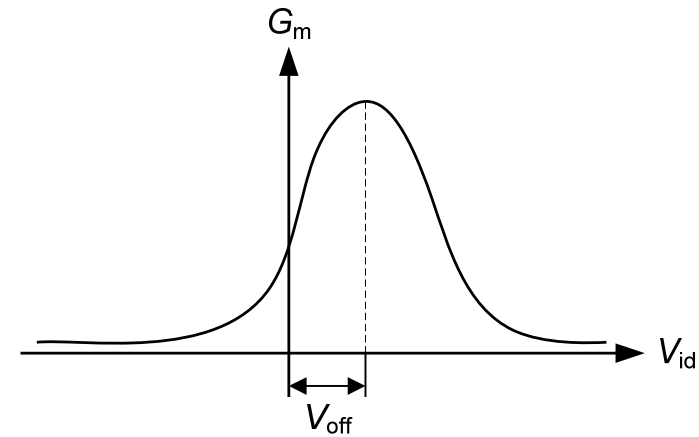
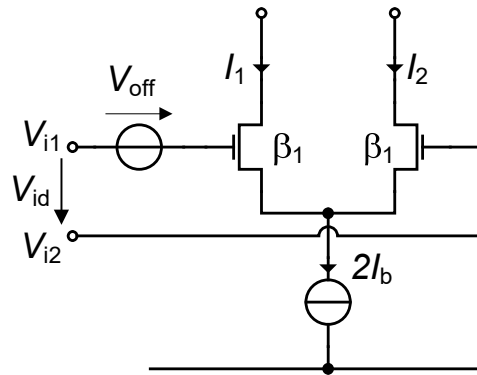
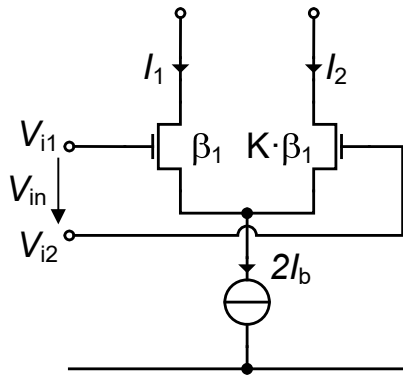


$$g_m = \frac{di_{od}}{dv_{id}} = \frac{G_m}{G_{m0}}$$

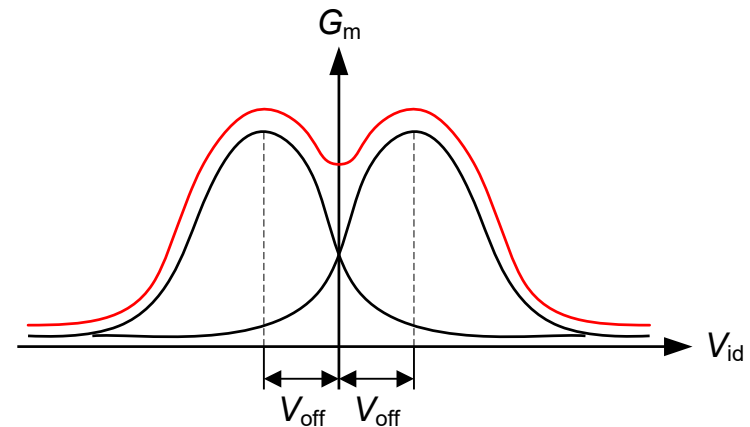
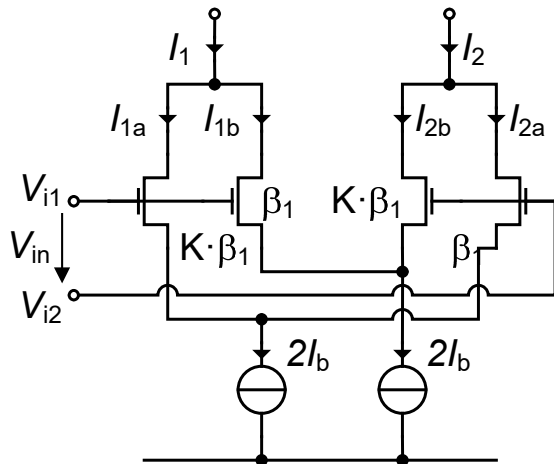


- Residual  $G_m$  ripple is minimum for  $\beta_1/\beta_3 \approx 2$
- Linear range extended by  $\sim 2x$

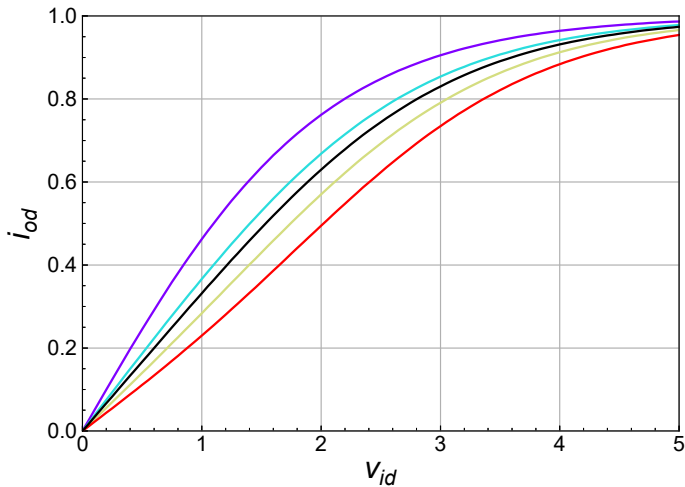
# Multi-tanh Linearization – Principle



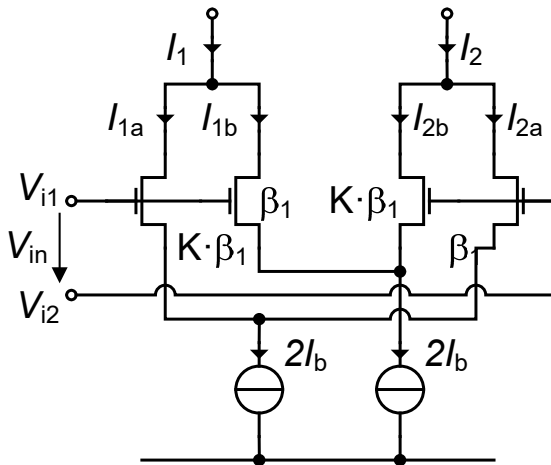
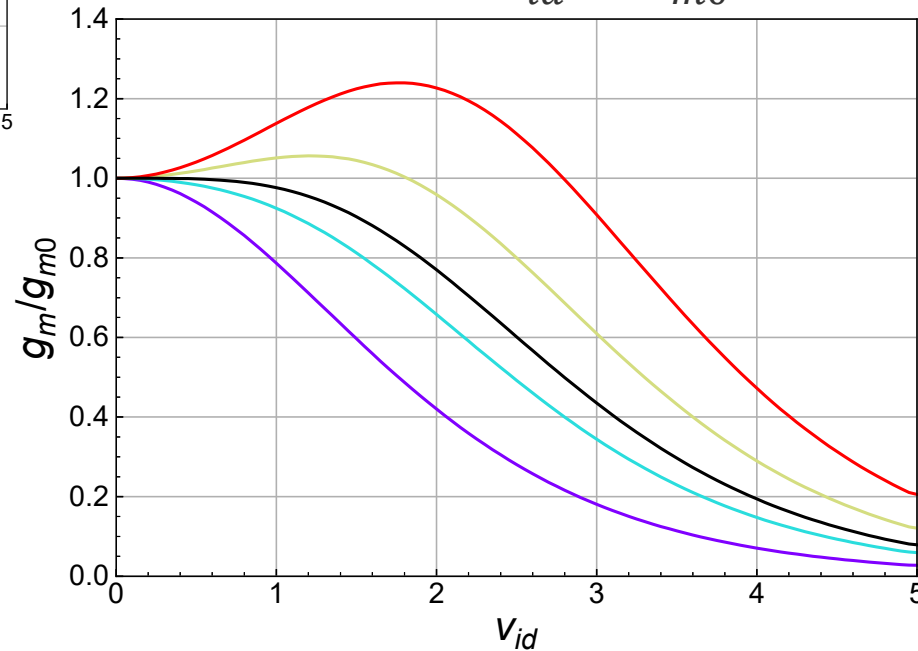
- Controlled offset voltage in weak inversion  $V_{off} = nU_T \cdot \ln K$
- Combination of two pairs with opposite offset voltages



# Multi-tanh Linearization – Example



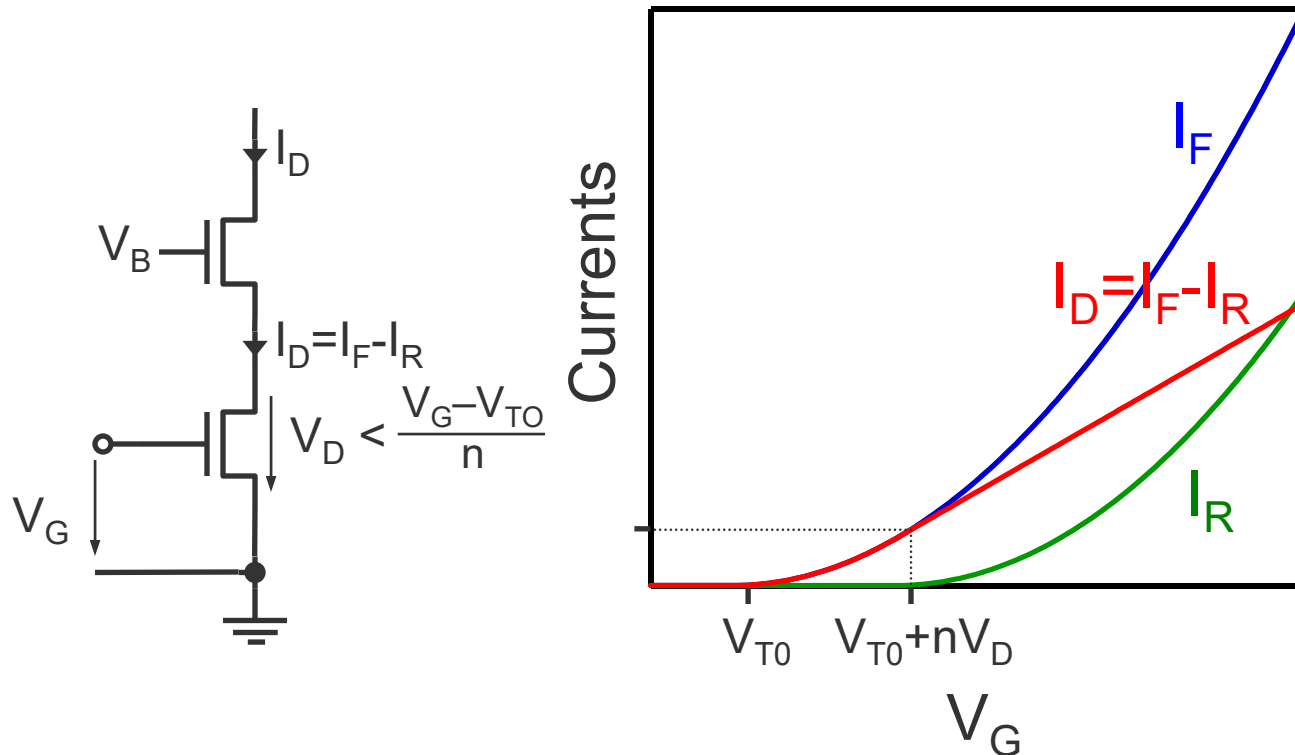
$$g_m = \frac{di_{od}}{dv_{id}} = \frac{G_m}{G_{m0}}$$



- For  $N = 2$  the residual  $G_m$  ripple is minimum for  $K = \beta_1/\beta_3 = 3.73$
- Linear range extended by almost 2x

# Linearization Based on MOSFET in Linear Region

- Particular case of square-law difference where the difference is done inside the same MOS transistor
- Achieves excellent linearity at the cost of higher noise factor



## Linearization Based on MOS in Linear Region

- M1 in the linear region  $I_D = \beta V_D \left( V_G - V_{T0} - \frac{n}{2} V_D \right)$  for  $V_D < V_P \cong \frac{V_G - V_{T0}}{n}$
- The transconductance is hence given by  $G_m = \beta V_D$
- Linear range defined by  $V_{Gmin} \geq V_{T0} + n \cdot V_D$  and  $V_{Gmax}$  limited by mobility degradation
- $V_D$  must be maintained constant to avoid any distortion
  - ▶ Cascode transistor and maximum  $G_{ms}$  for given current (i.e. weak inversion)
  - ▶ Distortion due to residual variations of  $V_D$
- The PSD of current fluctuations due to thermal noise (non-stationary) is given by

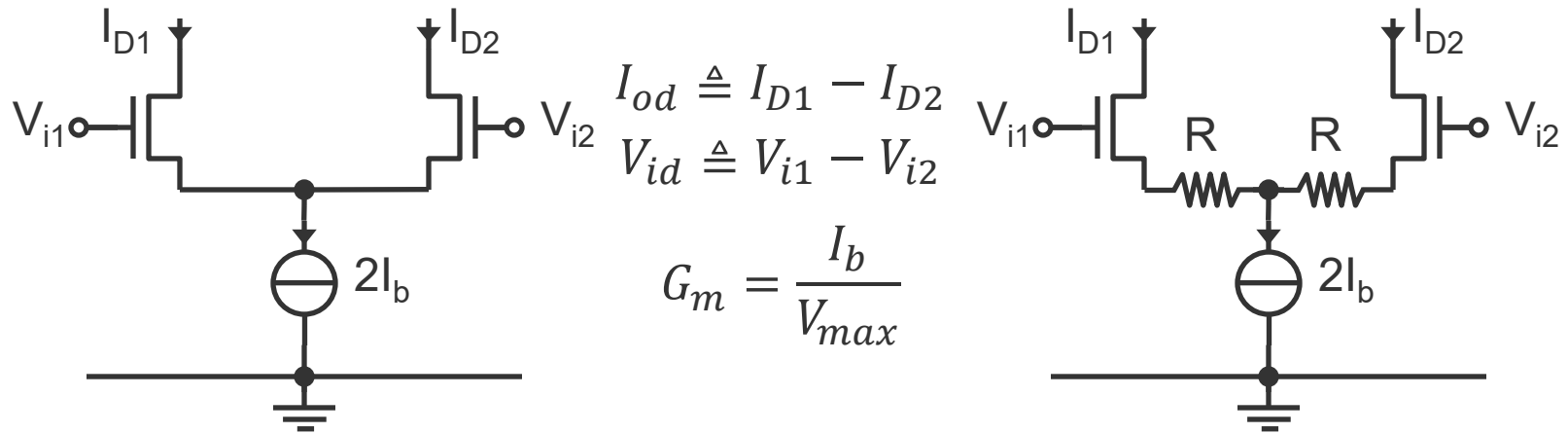
$$S_{\Delta I} = 4kT G_n \text{ with } G_n \cong G_{ms} = \beta(V_G - V_{T0})$$

- resulting in a **noise excess factor** given by

$$\gamma = \frac{G_n}{G_m} = \frac{\beta(\overline{V_G} - V_{T0})}{\beta V_D} = \frac{V_{Gmin} + \Delta V - V_{T0}}{V_D} \geq 1$$

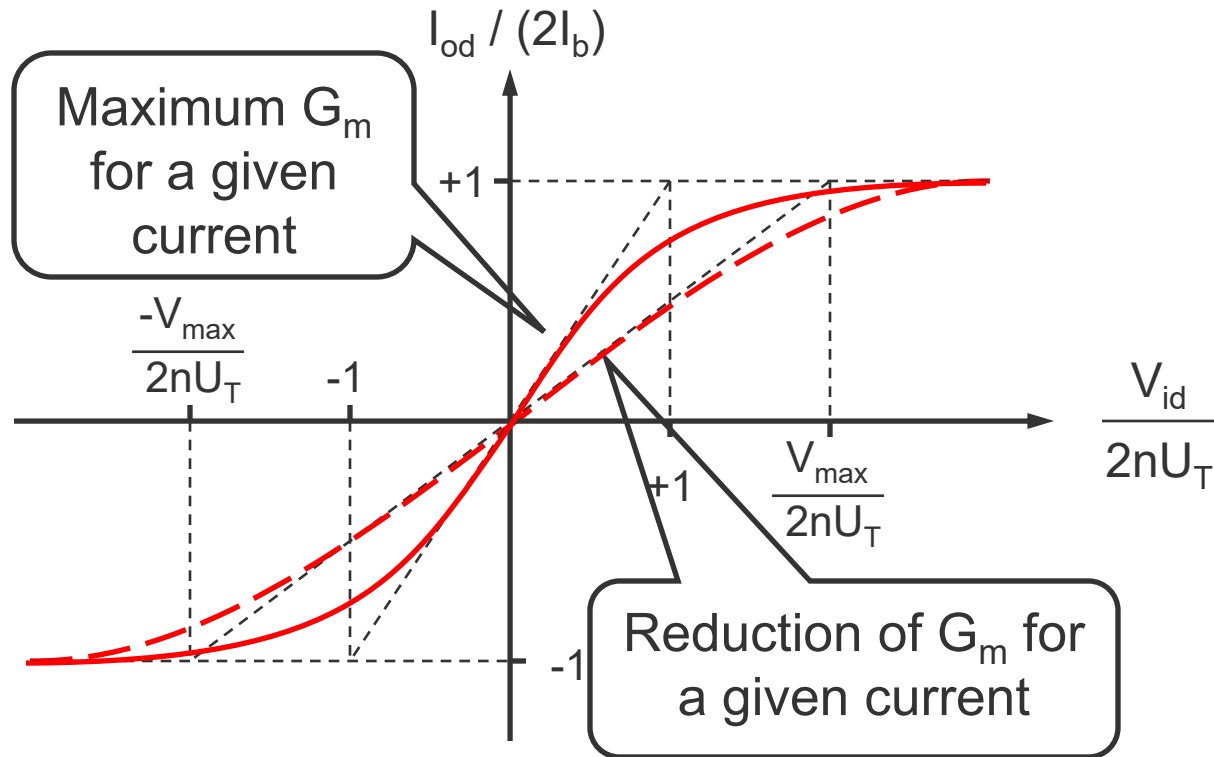
- Usually much larger than one since  $V_D < V_{Gmin} + \Delta V - V_{T0}$  where  $\Delta V$  is the signal amplitude resulting in a linearity versus noise trade-off

# Linearization vs Current Efficiency (1/2)



	Linear range $V_{max}$	Current efficiency $G_m/I_b$
Weak inversion	$2nU_T$	$\frac{1}{2nU_T}$
Strong inversion	$V_G - V_{T0}$	$\frac{1}{V_G - V_{T0}}$
Degenerated	$R \cdot I_b$	$\frac{1}{R \cdot I_b}$

# Linearization vs Current Efficiency (2/2)



$$G_{m,max} = \frac{I_b}{U_T}$$

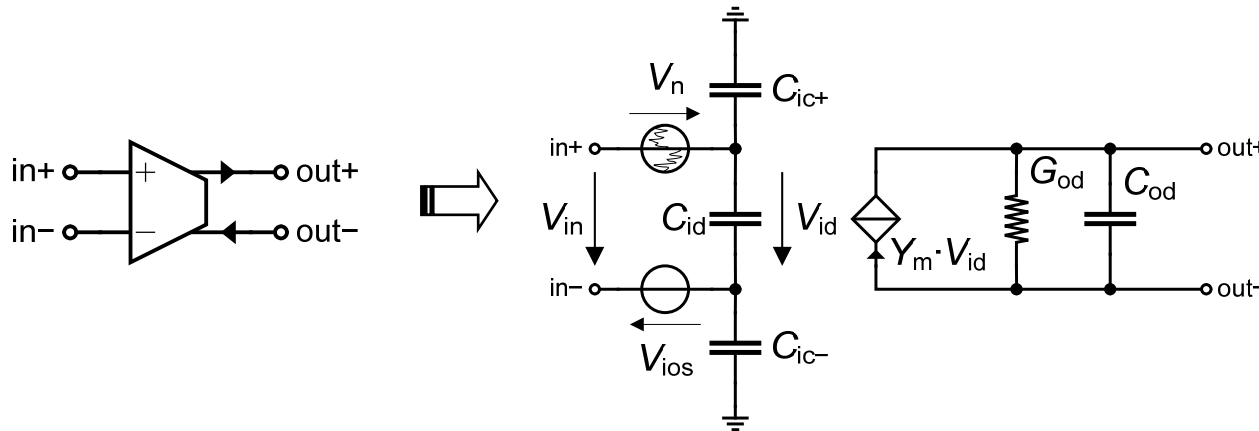
$$\xi = \frac{V_{max}}{2nU_T}$$

$$\frac{G_m}{G_{m,max}} = \frac{2nU_T}{V_{max}} = \frac{1}{\xi}$$

- Current efficiency  $G_m/I_b$  degrades proportionally to the increase of the linear range
- Results in power consumption increase for a required  $G_m$

# Linear Model of OTAs

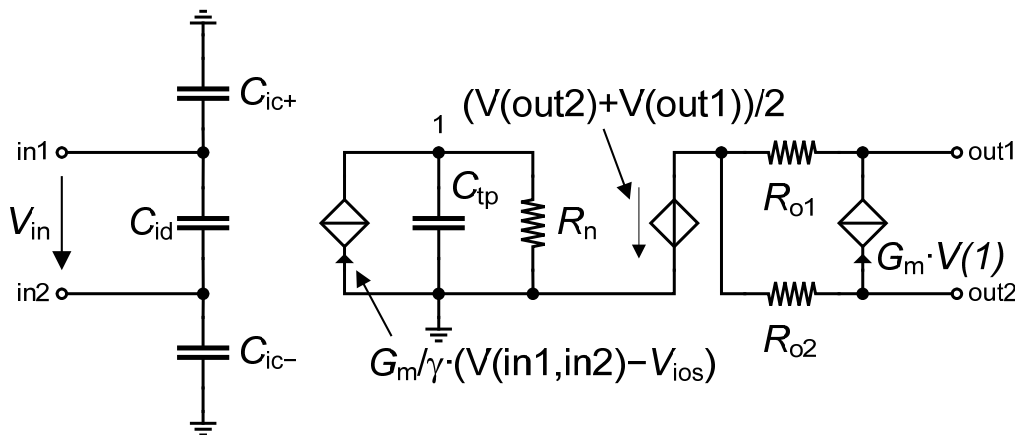
- An OTA can be modeled by the simple linear model given below



$$Y_m(s) = \frac{G_m}{1 + s \cdot \tau_p}$$

$$S_{V_n} = 4kT \cdot \frac{\gamma}{G_m}$$

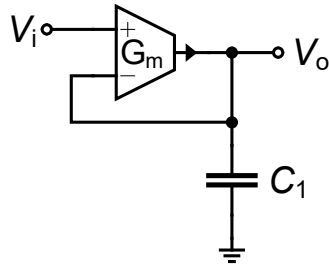
- Simple Spice implementation



$$R_n = \frac{\gamma}{G_m}$$

$$C_{tp} = \tau_p \cdot \frac{G_m}{\gamma}$$

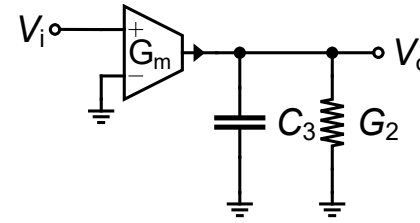
# First-order OTA LP Filters



- The transfer function of the above circuit is given by

$$T(s) \triangleq \frac{V_o}{V_i} = K \frac{\omega_c}{s + \omega_c}$$

- with  $K = 1$  and  $\omega_c = \frac{G_m}{C_1}$

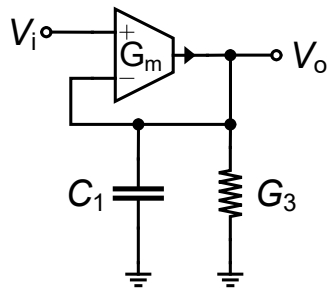


- The above alternative offers a dc gain different than one

$$T(s) \triangleq \frac{V_o}{V_i} = K \frac{\omega_c}{s + \omega_c}$$

- with  $K = \frac{G_m}{G_2}$  and  $\omega_c = \frac{G_2}{C_3}$

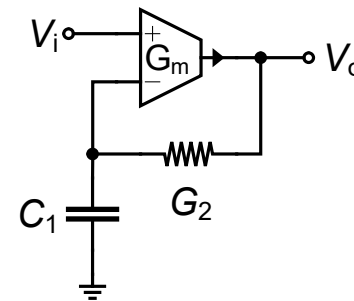
# First-order OTA LP Filters



- Another 1<sup>st</sup>-order LP section is shown above with a transfer function given by

$$T(s) \triangleq \frac{V_o}{V_i} = K \frac{\omega_c}{s + \omega_c}$$

- with  $K = \frac{G_m}{G_m + G_3}$  and  $\omega_c = \frac{G_m + G_3}{C_3}$

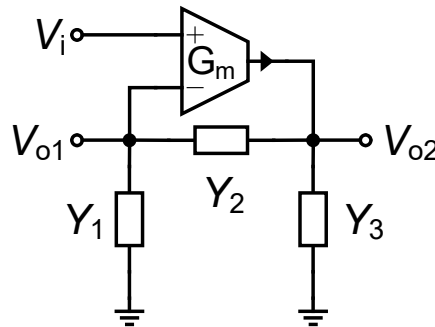


- The above circuit introduces an additional zero

$$T(s) \triangleq \frac{V_o}{V_i} = K \frac{s + \omega_z}{s + \omega_c}$$

- with  $K = \frac{G_m}{G_2}$ ,  $\omega_z = \frac{G_2}{C_1}$  and  $\omega_c = \frac{G_m}{C_1}$

# Generic Single OTA Filter



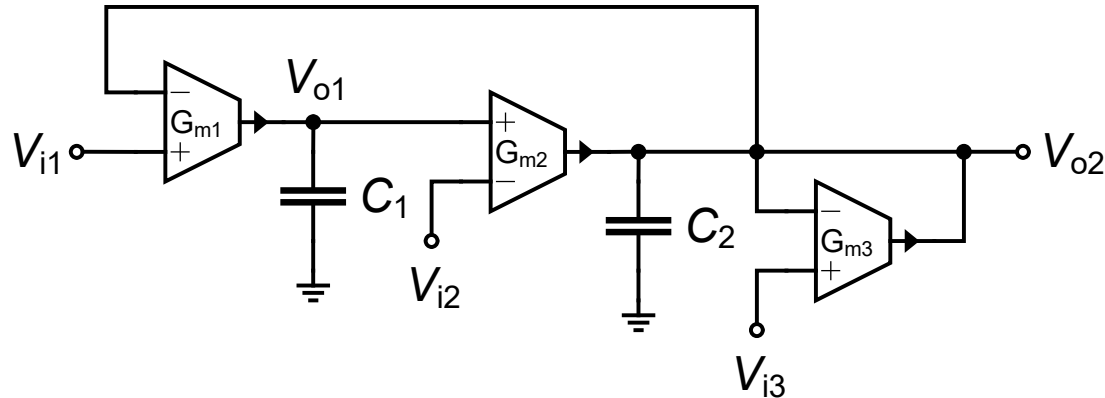
- All the previous circuits can be derived from the generic circuit shown above which has the following transfer functions

$$T_1(s) \triangleq \frac{V_{o1}}{V_i} = \frac{G_m Y_2}{Y_1 Y_2 + Y_1 Y_3 + Y_2 Y_3 + G_m Y_2}$$

$$T_2(s) \triangleq \frac{V_{o2}}{V_i} = \frac{G_m (Y_1 + Y_2)}{Y_1 Y_2 + Y_1 Y_3 + Y_2 Y_3 + G_m Y_2}$$

- The above 1<sup>st</sup>-order sections are obtained by replacing one of the admittances by a capacitor, one by a conductance and the remaining one either by a short or an open resulting in two passive component 1<sup>st</sup>-order sections

# The Tow-Thomas OTA-C Biquad



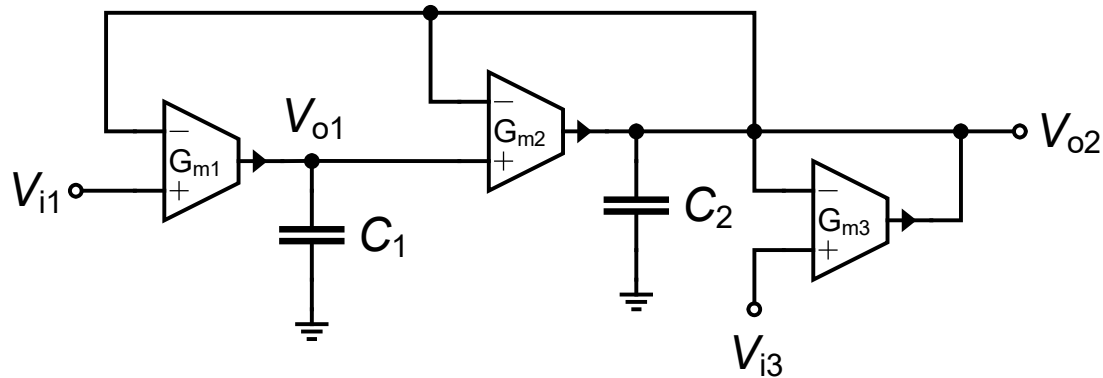
- The **Tow-Thomas** filter can also be realized with **OTAs** as shown above
- The various transfer functions are given by

$$V_{o1} = \frac{(\sigma\tau_2 + k_{22})V_{i1} + V_{i2} - k_{22}V_{i3}}{s^2\tau_1\tau_2 + k_{22}\sigma\tau_1 + 1}$$

$$V_{o2} = \frac{V_{i1} - \sigma\tau_1V_{i2} + k_{22}\sigma\tau_1V_{i3}}{s^2\tau_1\tau_2 + k_{22}\sigma\tau_1 + 1}$$

- with  $k_{22} = \frac{G_{m3}}{G_{m2}}$ ,  $\tau_1 = \frac{C_1}{G_{m1}}$  and  $\tau_2 = \frac{C_2}{G_{m2}}$
- This circuit is simple and has very **low sensitivity** and **low parasitic effects**

# The Feedback Lossy Integrator OTA-C Biquad



- This is a variant of the previous Tow-Thomas lossy integrators OTA biquad where the input of  $G_{m2}$  has been connected to its output (making it lossy)
- The output is then given by

$$V_{o1} = \frac{(s\tau_2 + k_{22})V_{i1} - (k_{22} - 1)V_{i3}}{s^2\tau_1\tau_2 + k_{22}s\tau_1 + 1}$$

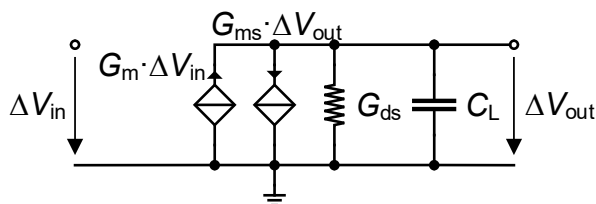
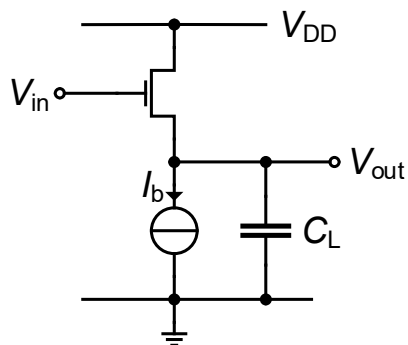
$$V_{o2} = \frac{V_{i1} + (k_{22} - 1)s\tau_1 V_{i3}}{s^2\tau_1\tau_2 + k_{22}s\tau_1 + 1}$$

- with  $k_{22} = 1 + \frac{G_{m3}}{G_{m2}}$ ,  $\tau_1 = \frac{C_1}{G_{m1}}$  and  $\tau_2 = \frac{C_2}{G_{m2}}$

# Outline

- Introduction
- RC-active filters
- MOSFET-C filters
- $G_m$ -C filters
- **Source-follower CTFs**
- Noise in CTFs
- Automatic tuning

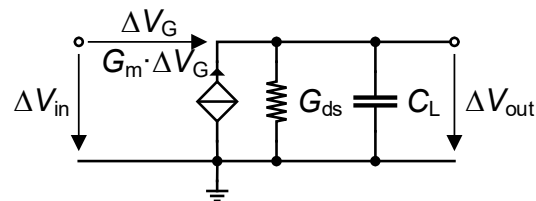
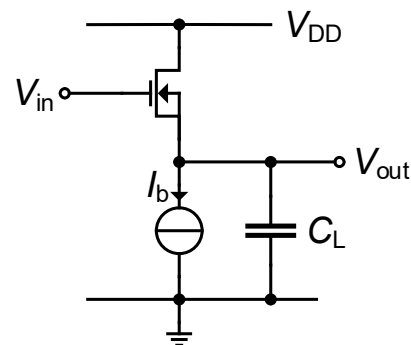
# Source-Follower Continuous-Time Filters



$$H(s) \triangleq \frac{\Delta V_{out}}{\Delta V_{in}} = \frac{A_{dc}}{1 + \frac{s}{\omega_c}}$$

$$A_{dc} = \frac{G_m}{G_{ms} + G_{ds}} \cong \frac{G_m}{G_{ms}} = \frac{1}{n}$$

$$\omega_c = \frac{G_{ms} + G_{ds}}{C_L} \cong \frac{G_{ms}}{C_L} = \frac{nG_m}{C_L}$$

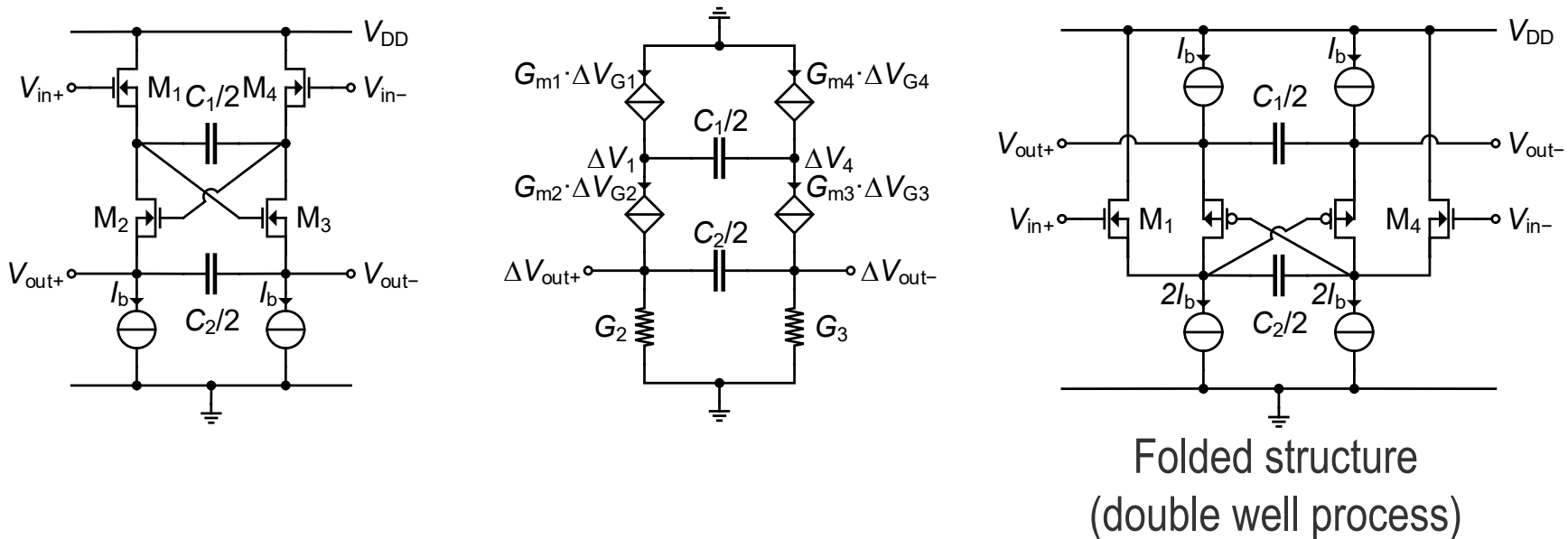


$$H(s) \triangleq \frac{\Delta V_{out}}{\Delta V_{in}} = \frac{A_{dc}}{1 + \frac{s}{\omega_c}}$$

$$A_{dc} = \frac{G_m}{G_m + G_{ds}} \cong 1$$

$$\omega_c = \frac{G_m + G_{ds}}{C_L} \cong \frac{G_m}{C_L}$$

# Source-Follower 2<sup>nd</sup>-order LP Filter

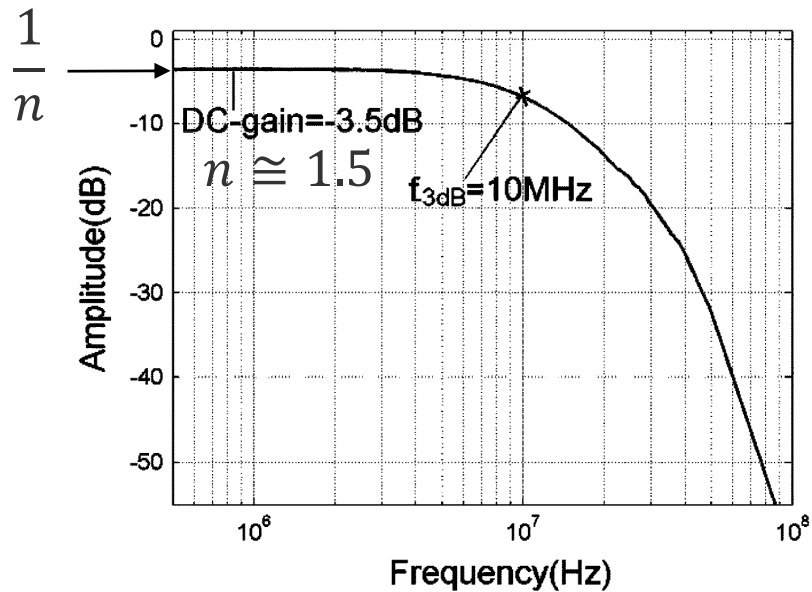
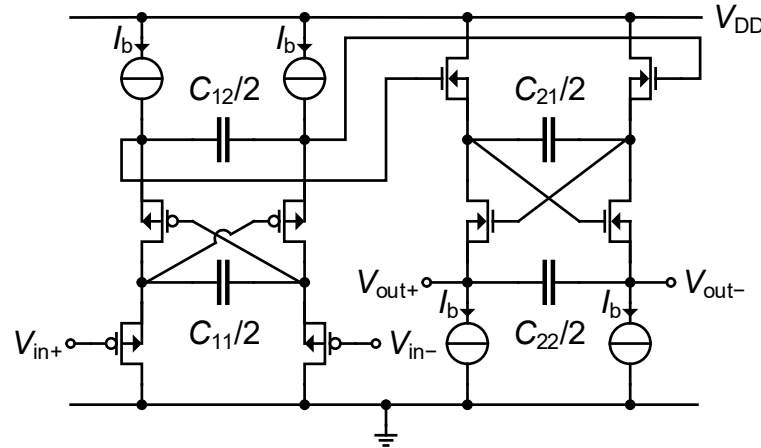


- The differential transfer function assuming  $G_{m1} = G_{m2} = G_{m3} = G_{m4} = G_m$  and neglecting the output conductances gives a 2<sup>nd</sup>-order LP filter

$$H_d(s) = \frac{1}{\left(\frac{s}{\omega_0}\right)^2 + \frac{s}{\omega_0 Q} + 1} \text{ with } \omega_0 = \frac{G_m}{\sqrt{C_1 C_2}} \text{ and } Q = \sqrt{\frac{C_2}{C_1}}$$

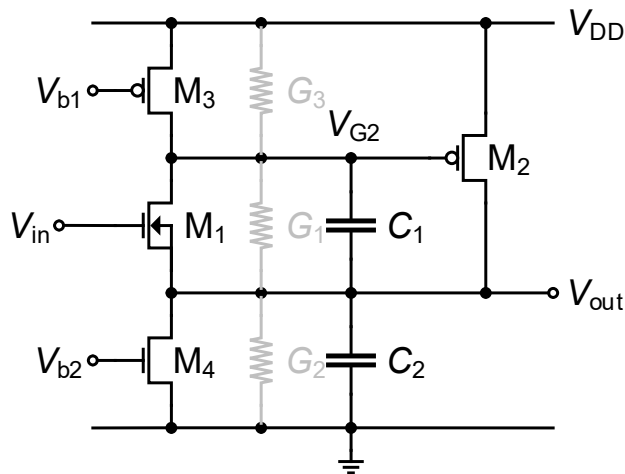
- The transfer function slightly changes if the transistors are in the common substrate due to the substrate effect

# A Fourth-Order SF Continuous-Time Filter



Technology	CMOS 0.18 $\mu\text{m}$
Die Area	0.26mm <sup>2</sup> x2
Power supply	1.8V
Current consumption	2.28mA
Power consumption	4.1mW
DC-gain	-3.5dB
$f_{-3dB}$	10MHz
$f_{-3dB}$ tuning range	$\pm 40\%$
IRN	7.5nV/ Hz
$V_{in,noise}$	24 $\mu\text{V}_{rms}$
DR (HD3=-40dB)	79dB
in-band IIP3 ( $f_1=3\text{MHz}$ , $f_2=4\text{MHz}$ )	17.5dBm
1dBcp	5dBm
HD3 (600mV <sub>pp</sub> @3MHz)	-40dB

# Super-Source-Follower (SSF) Filters



$$H(s) = \frac{1}{\left(\frac{s}{\omega_0}\right)^2 + \frac{s}{\omega_0 Q} + 1}$$

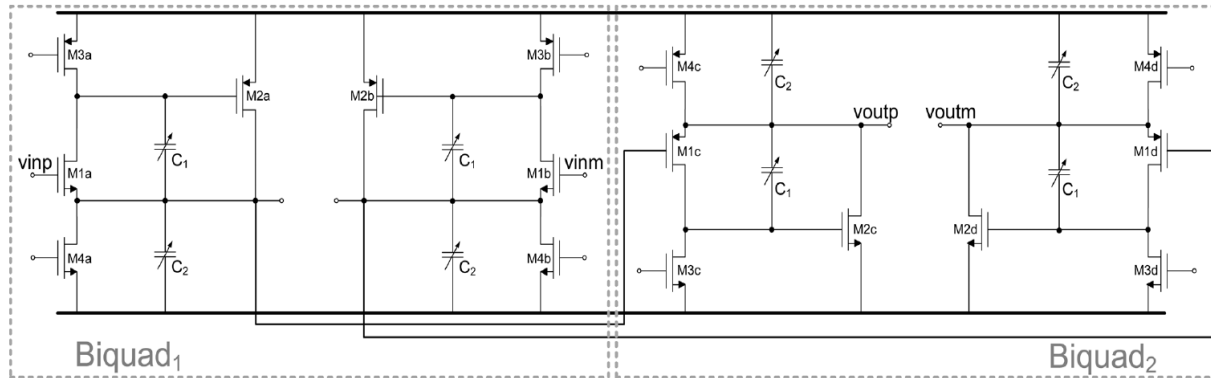
$$\text{with } \omega_0 = \sqrt{\frac{G_{m1} G_{m2}}{C_1 C_2}} \text{ and } Q = \sqrt{\frac{G_{m1} C_2}{G_{m2} C_1}}$$

- It is important to put M1 into a separate well to avoid any substrate effects
- The dc gain accounting for the output conductances is given by

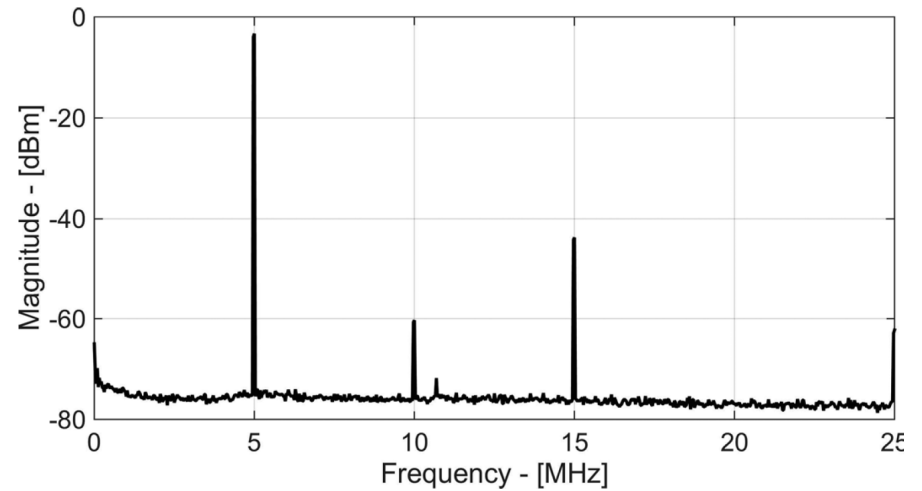
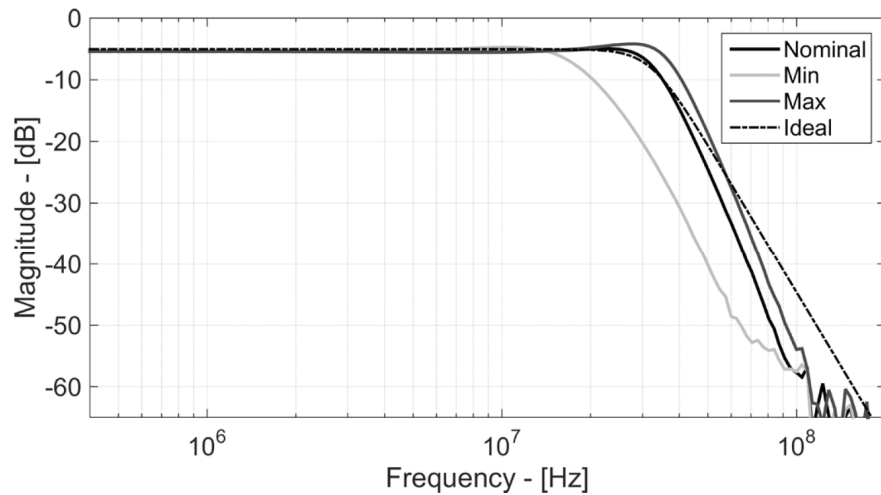
$$H_{dc} \cong \frac{1 + \frac{G_3}{G_{m2}}}{1 + \frac{G_3}{G_{m2}} + \frac{G_1}{G_{m1}}} \cong 1$$

- for  $G_1 \ll G_{m1}$  and  $G_3 \ll G_{m2}$

# Fourth-order Low-pass SSF Filter

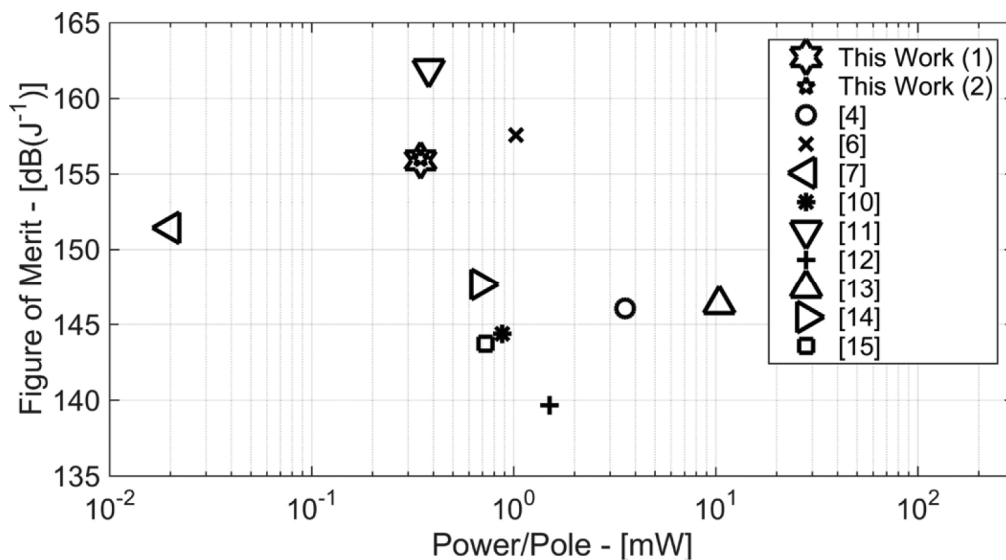


Parameter	Biquad <sub>1</sub>	Biquad <sub>2</sub>
Poles Frequency – $f_0$	33 MHz	33 MHz
Poles Quality Factor – $Q$	0.5412	1.3066
$g_{m1}$	1.8 mA/V	1.8 mA/V
$g_{m2}$	1.8 mA/V	1.8 mA/V
$C_1$	15 pF	6.2 pF
$C_2$	4.4 pF	10 pF



# Benchmark

Parameters	This work	[4]	[6]	[7]	[10]	[11]	[12]	[13]	[14]	[15]
Technology [nm]	180	130	180	130	130	90	130	130	180	180
Supply voltage [V]	1.8	1.2	1.8	1.2	0.55	1.2	1	1.2	1.8	1.5
Order	4	4	4	6	4	6	5	2	6	6
Topology	SSF-based	Active-g <sub>m</sub> -RC	SF-based	SF-based	Active-g <sub>m</sub> -RC	Active-RC	Active-RC	OTA-C	Active-RC	g <sub>m</sub> -C
f <sub>0</sub> [MHz]	33	11	10	280	11.3	255	20	200	500	13.5
Power [mW]	1.38	14.2	4.1	0.12	3.5	2.28	7.5	20.8	4.1	4.35
Power/Pole [mW]	0.34	3.55	0.88	0.26	1	0.02	1.5	10.4	0.68	0.73
IIP3 [dBm]	18 - 1	21	7.5	11	10	14	26	14	15.9	22
f <sub>IM3L</sub> [MHz]	1 - 14	0.5	2	1	2	60	0.27	149.7	5	1
f <sub>IM3L</sub> /f <sub>0</sub>	0.03 - 0.42	0.04	0.2	0.004	0.18	0.24	0.014	0.75	0.01	0.074
In-Band Integrated Noise [μV <sub>RMS</sub> ]	45	36	23.7	368	110	200	232	494	293	335
Area [mm <sup>2</sup> ]	0.14	0.9	0.43	0.06	0.52	0.018	1.53	0.5	0.23	1
FoM <sub>conv</sub> [dB(J <sup>-1</sup> )]	171.1 - 159.8	159.5	164.6	175.9	151.9	168.2	158.4	147.6	167.7	155
FoM [dB(J <sup>-1</sup> )]	155.9 - 156	146.1	157.6	151.4	144.4	162	139.7	146.3	147.7	143.7



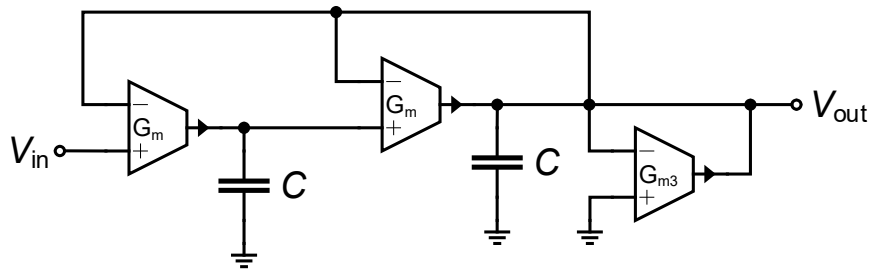
$$FoM = 10 \log_{10} \left( \frac{IMFDR_3 f_{@-3 \text{ dB}} N}{P_W} \cdot \left[ \frac{f_{IM3L}}{f_{poles}} \right] \right)$$

- [4] S. D'Amico, V. Giannini, and A. Baschiroto, "A 4th-order active-Gm-RC reconfigurable (UMTS/WLAN) filter," *IEEE J. Solid-State Circuits*, vol. 41, no. 7, pp. 1630-1637, Jul. 2006.
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- [6] S. D'Amico, M. Conta, and A. Baschiroto, "A 4.1-mW 10-MHz fourth-order source-follower-based continuous-time filter with 79-dB DR," *IEEE J. Solid-State Circuits*, vol. 41, no. 12, pp. 2713-2719, Dec. 2006.
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- [13] M. Mobarak, M. Onabajo, J. Silva-Martinez, and E. Sanchez-Sinencio, "Attenuation-predistortion linearization of CMOS OTAs with digital correction of process variations in OTA-C filter applications," *IEEE J. Solid-State Circuits*, vol. 45, no. 2, pp. 351-367, Feb. 2010.
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- [15] M. Oskooei, N. Masoumi, M. Kamarei, and H. Sjolund, "A CMOS 4.35-mW +22-dBm IIP3 continuously tunable channel select filter for WLAN/WIMAX receivers," *IEEE J. Solid-State Circuits*, vol. 46, no. 6, pp. 1382-1391, Jun. 2011.

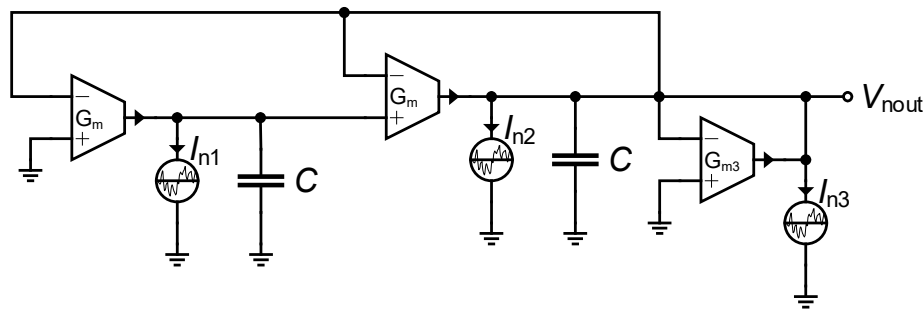
# Outline

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- Automatic tuning

# Noise in $G_m$ -C Tow-Thomas Biquad



$$G_{m1} = G_{m2} = G_m \text{ and } C_1 = C_2 = C$$



$$H(s) \triangleq \frac{V_{out}}{V_{in}} = \frac{1}{\left(\frac{s}{\omega_0}\right)^2 + \frac{s}{\omega_0 Q} + 1}$$

$$\text{with } \omega_0 = \frac{G_m}{C} \text{ and } Q = \frac{G_m}{G_m + G_{m3}}$$

$$R_{m1}(s) \triangleq \frac{V_{nout}}{I_{n1}} = -\frac{1}{G_m} \cdot \frac{1}{\left(\frac{s}{\omega_0}\right)^2 + \frac{s}{\omega_0 Q} + 1}$$

$$R_{m2}(s) \triangleq \frac{V_{nout}}{I_{n2}} = -\frac{1}{G_m} \cdot \frac{\frac{s}{\omega_0}}{\left(\frac{s}{\omega_0}\right)^2 + \frac{s}{\omega_0 Q} + 1}$$

$$R_{m3}(s) \triangleq \frac{V_{nout}}{I_{n3}} = R_{m2}(s)$$

$$S_{V_{out}^2} = |R_{m1}(f)|^2 \cdot S_{I_{n1}} + |R_{m2}(f)|^2 \cdot (S_{I_{n2}} + S_{I_{n3}})$$

$$S_{I_{ni}} = 4k_B T \cdot \gamma_{ni} \cdot G_{mi} \text{ for } i = 1, 2, 3 \text{ (ignoring flicker noise)}$$

## Noise in $G_m$ -C Tow-Thomas Biquad

- Considering only thermal noise, the equivalent noise bandwidth for noise sources  $I_{n1}$ ,  $I_{n2}$  and  $I_{n3}$  are given by

$$B_{n1} = Q \cdot \frac{\omega_0}{4} \text{ and } B_{n2} = B_{n3} = \frac{\omega_0}{4}$$

- The corresponding output thermal noise voltage is given by

$$V_{nout}^2 \Big|_{I_{n1}} = 4k_B T \cdot \gamma_{n1} G_m \cdot \frac{1}{G_m^2} \cdot B_{n1} = \frac{\gamma_{n1} k_B T}{C} \cdot Q$$

$$V_{nout}^2 \Big|_{I_{n2}, I_{n3}} = 4k_B T \cdot \gamma_{n2} G_m \cdot \frac{1}{G_m^2} \cdot B_{n2} = \frac{\gamma_{n2} k_B T}{C}$$

- The total output thermal noise voltage

$$V_{nout}^2 = \frac{k_B T}{C} \cdot (\gamma_{n1} Q + \gamma_{n2} + \gamma_{n3})$$

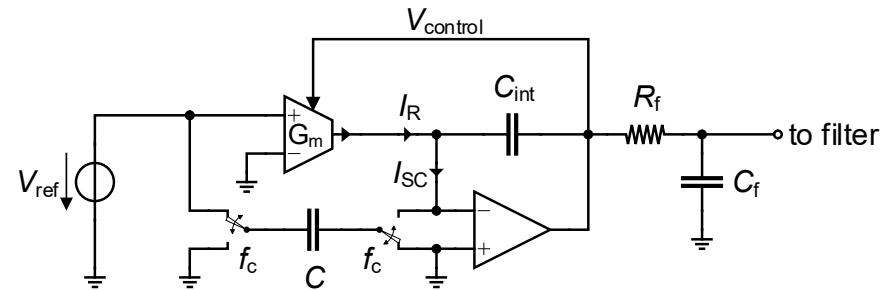
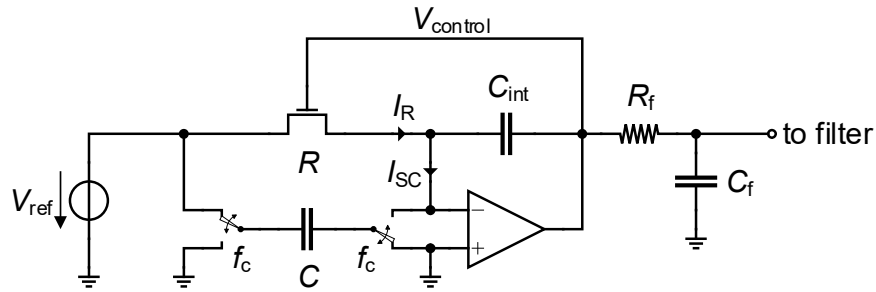
# Outline

- Introduction
- RC-active filters
- MOSFET-C filters
- $G_m$ -C filters
- Source-follower CTFs
- Noise in CTFs
- **Automatic tuning**

# Component Accuracy and Automatic Tuning Control

- Component mismatch on-chip remains small
  - ▶  $\frac{\Delta C}{C} \sim 0.05 \%$
  - ▶  $\frac{\Delta R}{R} \sim 2 \%$
  - ▶  $\frac{\Delta G_m}{G_m} \sim 10 \%$  (often due to bias current mismatch)
- However, absolute errors can be very large
  - ▶ RC time constants only accurate to 20-50 %
  - ▶  $C/G_m$  time constants even less accurate
- Tuning control circuit is needed to obtain 1-5% accuracy in filter time constants
- Tuning control circuits rely on tight matching between a reference circuit in the control loop and the filter to be tuned
- An external clock signal of precisely controlled frequency is commonly used as reference signal

# Simple SC Control Circuit



- Assuming an ideal OPAMP we then have

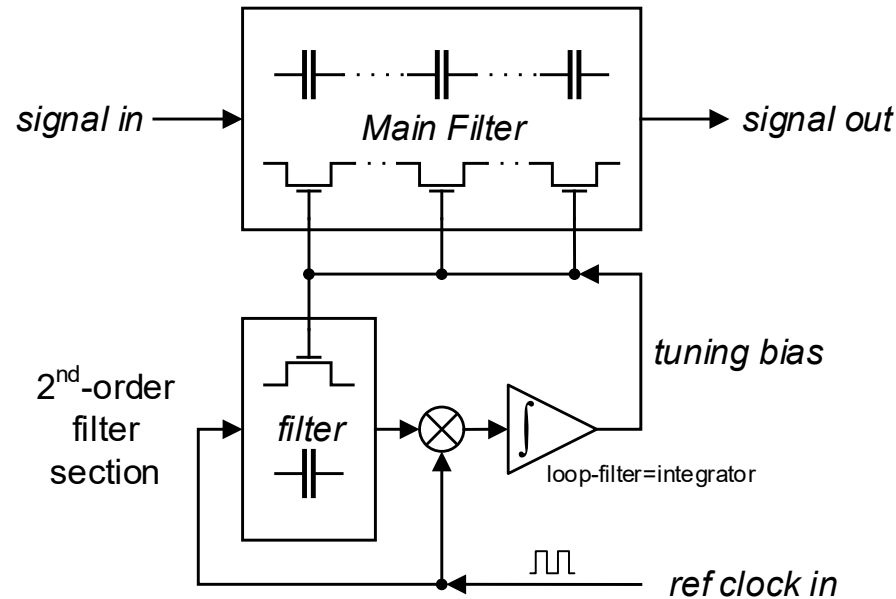
$$I_R = \frac{V_{ref}}{R} \text{ and } \overline{I_{SC}} = f_c \cdot C \cdot V_{ref}$$

- The circuit imposes that  $I_R = \overline{I_{SC}}$  and hence

$$R \cdot C = \frac{1}{f_c}$$

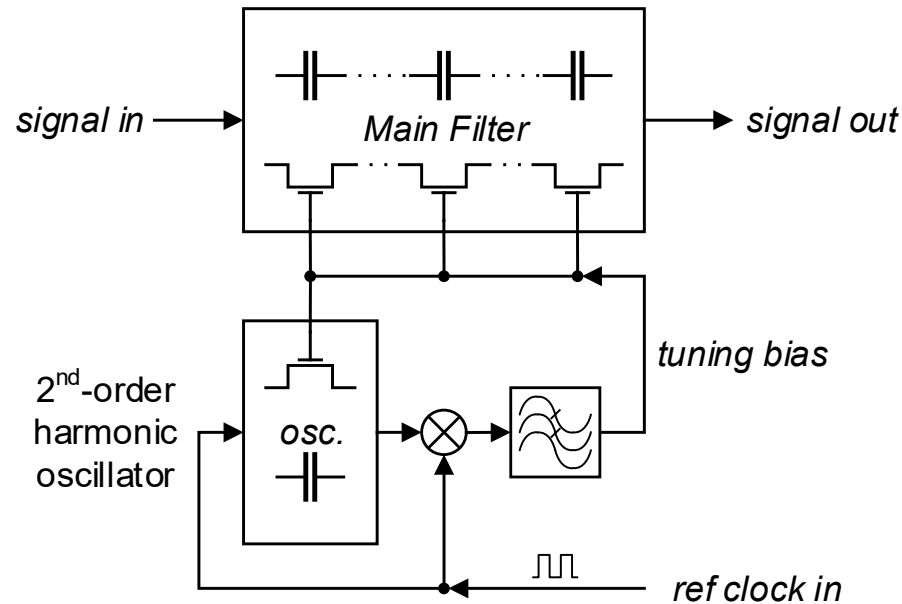
- Accuracy is limited to a few percent by
  - clock feedthrough in the MOS switches
  - OPAMP or OTA offset and speed
  - Imperfect matching between R, C in the control circuit and R,C's in the filter
- For  $G_m$ -C filters, the MOSFET resistor is simply replaced by a transconductor

# PLL with Voltage-controlled Filter (VCF)



- The phase of the auxiliary filter output signal is compared to that of the reference clock signal and the tuning bias is adjusted until the two differ by a predetermined value (i.e.  $\pi/2$ )

# PLL with Voltage-controlled Oscillator (VCO)



- The frequency (i.e. phase variations) of the oscillator's output signal is compared to that of the clock reference signal

# Example of $G_m$ -C Filter with Automatic Tuning

